



the
abdus salam
international centre for theoretical physics

ICTP 40th Anniversary

*SCHOOL ON SYNCHROTRON RADIATION AND APPLICATIONS
In memory of J.C. Fuggle & L. Fonda*

19 April - 21 May 2004

Miramare - Trieste, Italy

1561/36

Photo emission electron microscopy - Outline

E. Bauer

Photo emission electron microscopy

Outline

Introduction

Electron optics

Resolution

Transmission

Instruments

PEEM

PEEM + LEEM

Methodic

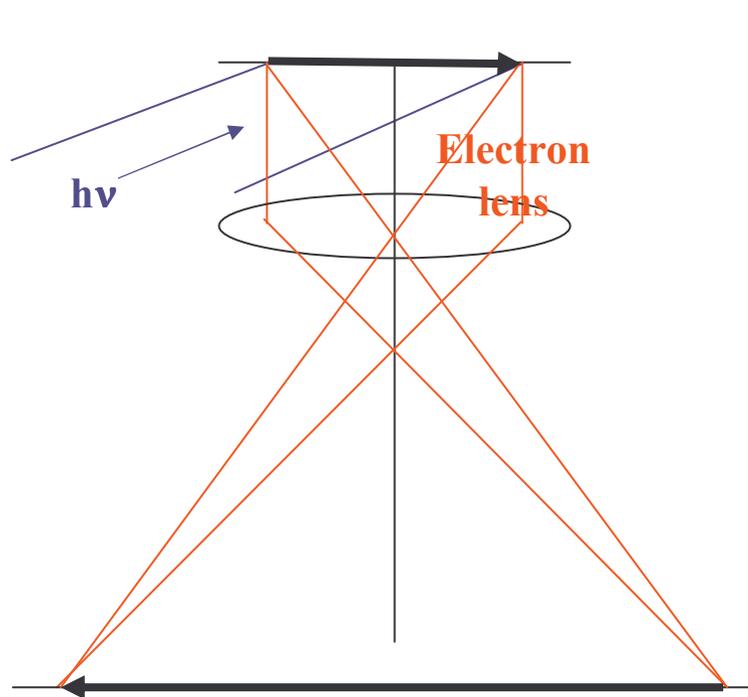
Application examples

Chemical imaging

Magnetic imaging

Photo Emission Electron Microscopy (PEEM)

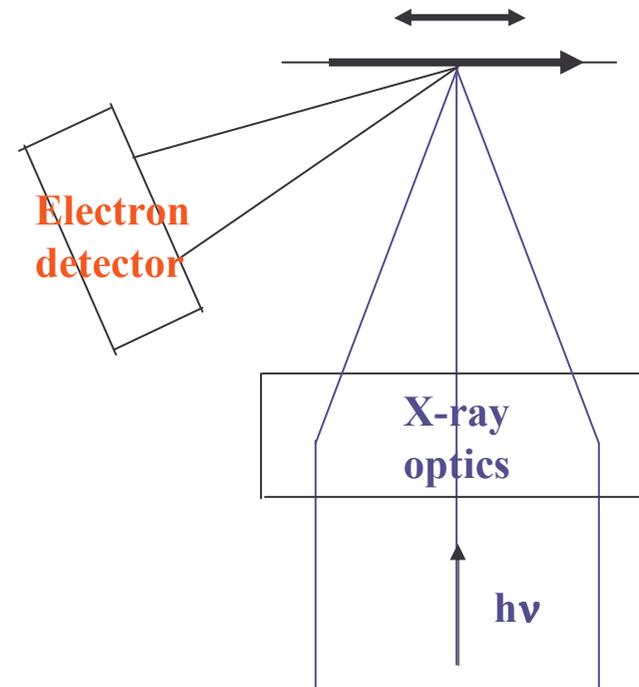
2 types



broad illumination

**Full field
sample fixed**

Bauer



focused illumination

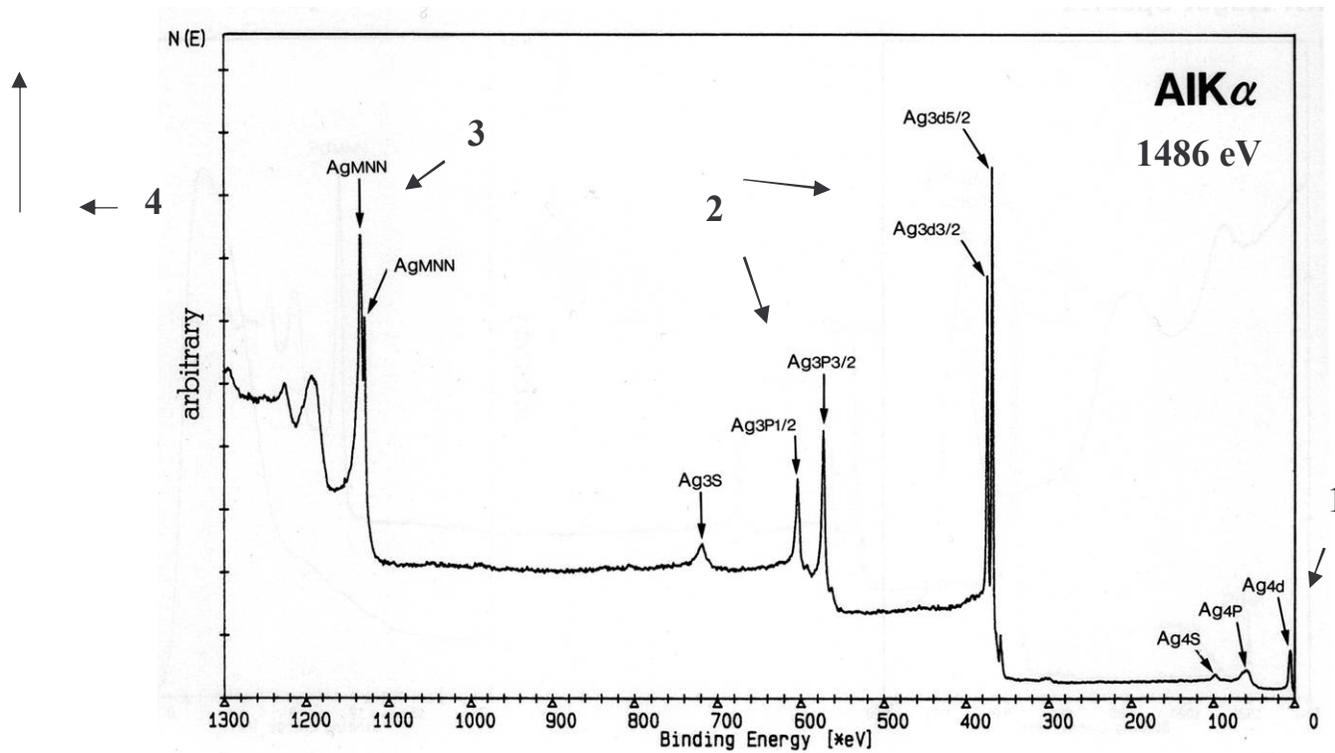
**Scanning
sample scanned**

Kiskinova

PEEM

4 imaging modes

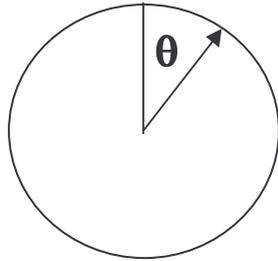
- | | | | |
|---|--------------------------|------------------------|----------------------|
| 1 | Threshold UV- and X-PEEM | Photoelectrons PE | } with energy filter |
| 2 | XPEEM | “ | |
| 3 | XAEEM | Auger electrons AE | |
| 4 | XSEEM | Secondary electrons SE | |



Angular distribution

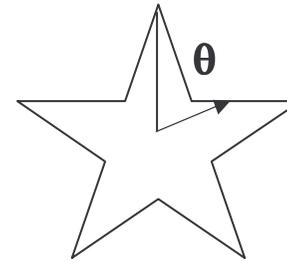
Internal

Amorphous, polycrystalline, SE



$$I_i(\theta) = \text{const.}$$

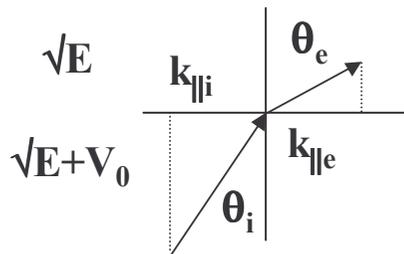
single crystalline, PE, AE



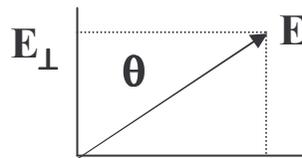
$I_i(\theta)$ due to diffraction

Internal (i) → External (e)

$n \sim$ Refraction



k_{\parallel} conservation $k_{\parallel e} = k_{\parallel i}$



$$E_{\perp} = E \cos \theta$$

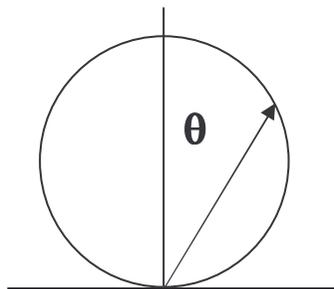
For escape necessary:

$E_{\perp} > \Phi$ (work function)

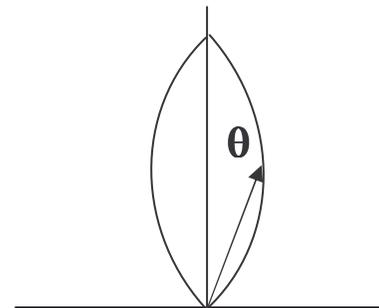
I (ionization energy)

U (HOMO)

External



$$I_e(\theta) = \cos \theta$$



Electron optics

The cathode lens

In emission microscopy θ is large

Electron lenses can accept only small θ because of large chromatic and spherical aberrations

Solution of problem: accelerate electrons to high energy before lens \rightarrow

Immersion objective lens = cathode lens

$$n \sin\theta = \text{const}$$

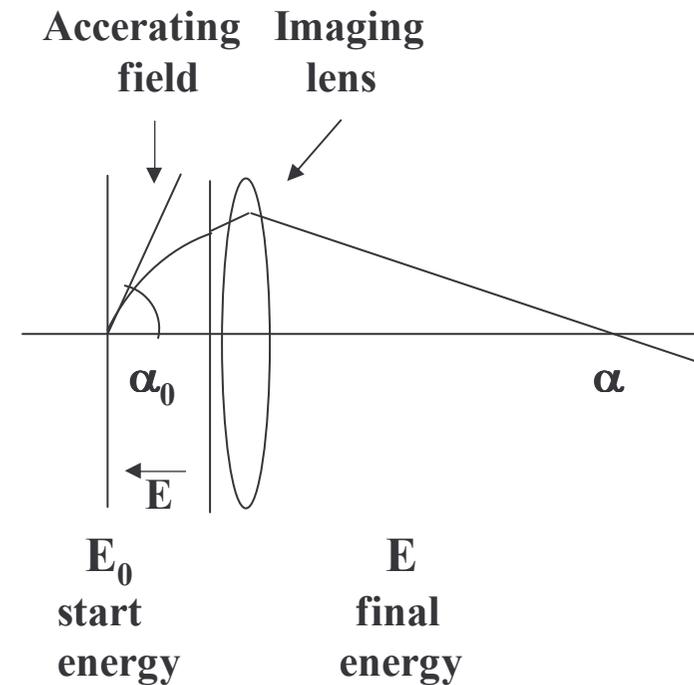
$$n \sim v \sim \sqrt{E}$$

$$\theta \rightarrow \alpha$$

$$\sin \alpha / \sin \alpha_0 = \sqrt{E_0 / E}$$

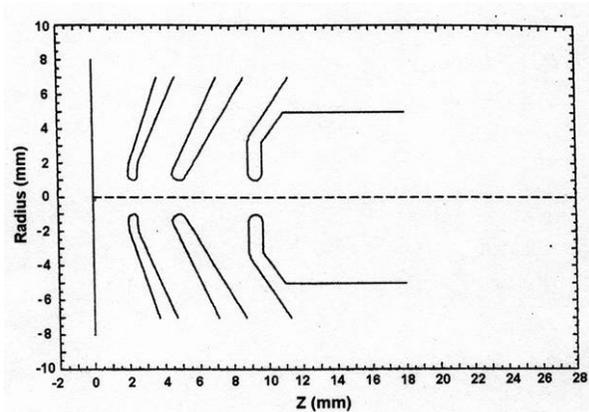
Example for $E = 20000 \text{ eV}$:

| | | |
|------------------------------------|------|--------|
| E_0 | 2 eV | 200 eV |
| α for $\alpha_0 = 45^\circ$ | 0.4° | 4.5° |

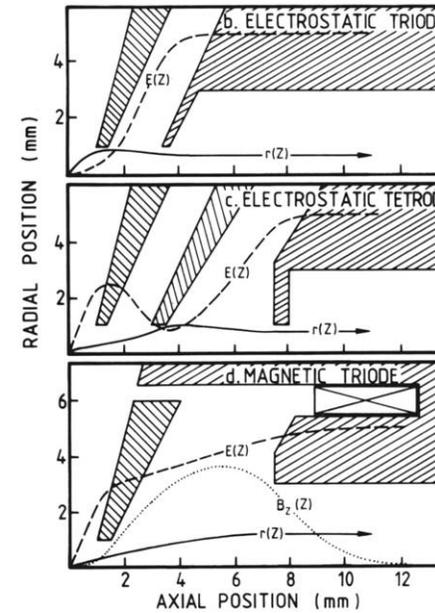


Cathode lens types

Electrostatic tetrode

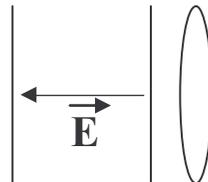


Lens comparison



Estimation of aberrations:

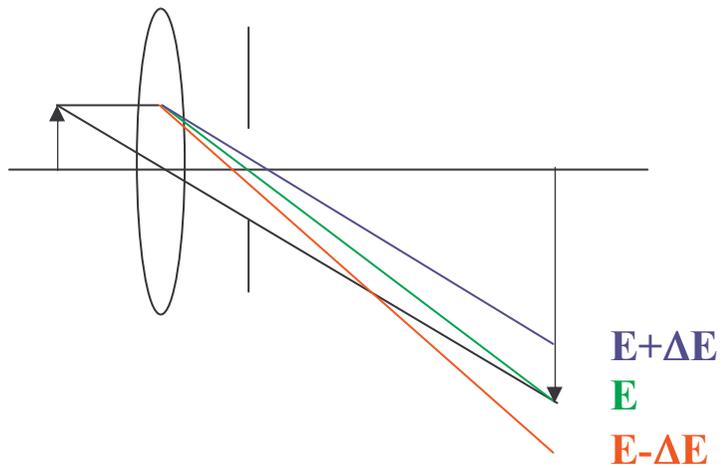
Separate lens into acceleration and imaging regions



At low energies aberrations of accelerating region dominates

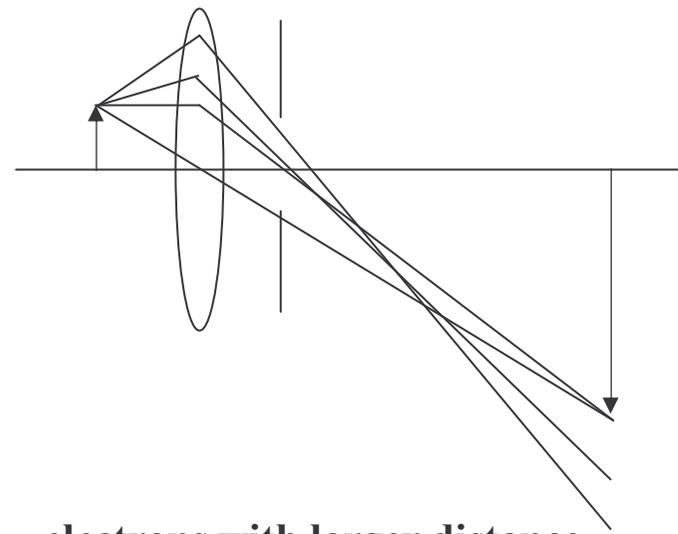
Aberrations

chromatic



**slower (faster) electrons
are more (less) deflected**

spherical

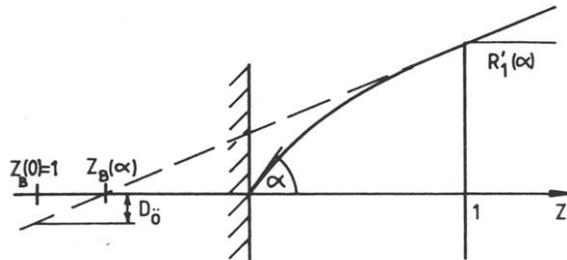


**electrons with larger distance
from axis are more deflected
(stronger field!)**

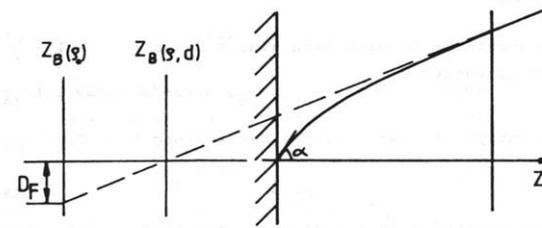
Aberrations of homogeneous acceleration field

$$\rho_0 = E_0/E \quad \varepsilon = \Delta E_0/E \quad \rho = \rho_0 + \varepsilon$$

Spherical aberration $D_{\ddot{0}}$



Chromatic aberration D_F



Approximation: ρ_0 and $\varepsilon \ll 1/\cos \alpha^2 > 1$

Example: $E_0 = 100 \text{ eV}$, $\Delta E_0 = 1 \text{ eV}$, $E = 20000 \text{ eV}$

$$\varepsilon = \rho_0 / 100, \quad \rho_0 = 1/200$$

$$D_{\ddot{0}} \approx 2 \rho \sin \alpha (1 - \cos \alpha)$$

$$\approx \rho \alpha^3 \text{ for small } \alpha$$

$$D_F \approx 2 \rho \sin \alpha (\sqrt{\rho_0 / \rho} - 1)$$

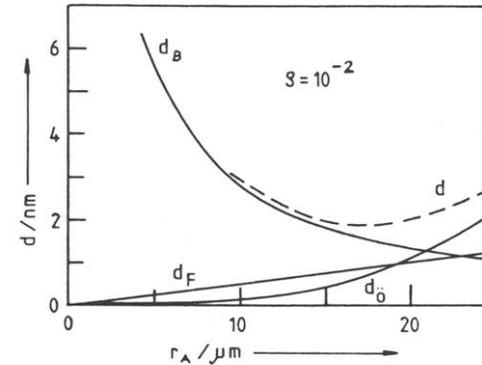
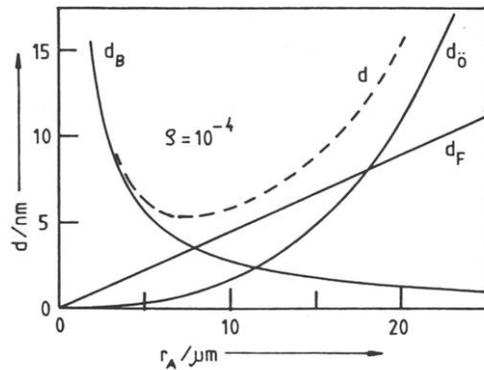
$$\approx \varepsilon \sin \alpha \text{ for } \varepsilon \ll \rho_0$$

$$\approx \varepsilon \alpha \text{ for small } \alpha$$

α -dependent aberrations require α -limitation by angle-limiting aperture (“contrast aperture”) with radius r_A

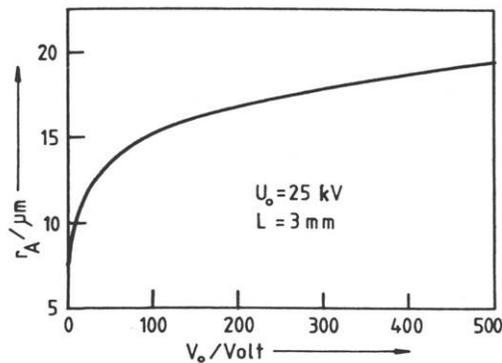


Diffraction by aperture: diffraction disc of confusion $d_B = 0.6 \lambda / r_A$
 Approximate resolution $d = \sqrt{d_{\ddot{o}}^2 + d_F^2 + d_B^2}$

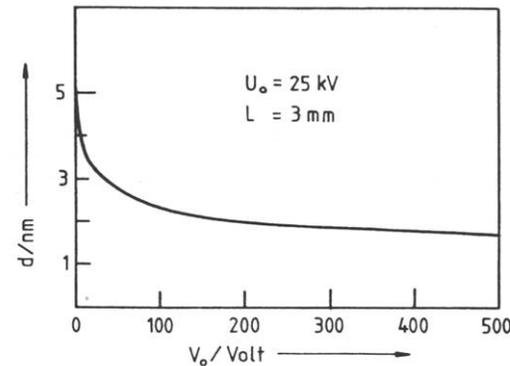


$L = 3 \text{ mm}$ $E = 25000 \text{ eV}$ $\Delta E_0 = 0.25 \text{ eV}$

Optimum aperture radius



Optimum resolution



Note: small angle approximation $\sin \alpha \approx \alpha \sim r$

Transmission

limited by angle accepted by contrast aperture (r_A)

Axial distance (in back focal plane) of electron starting at angle α

$$r \approx f \sin \alpha \sqrt{E_0/E} \quad (f \text{ focal length})$$



$$\sin \alpha \approx (r/f) \sqrt{E_0/E}$$

Examples for $f = 10 \text{ mm}$, $E = 20000 \text{ eV}$, $r_A = 10 \text{ } \mu\text{m}$

| | | |
|---------------|-------|--------|
| E_0 | 2 eV | 200 eV |
| $\sin \alpha$ | 0.2 | 0.02 |
| α | 11.5° | 1.15° |

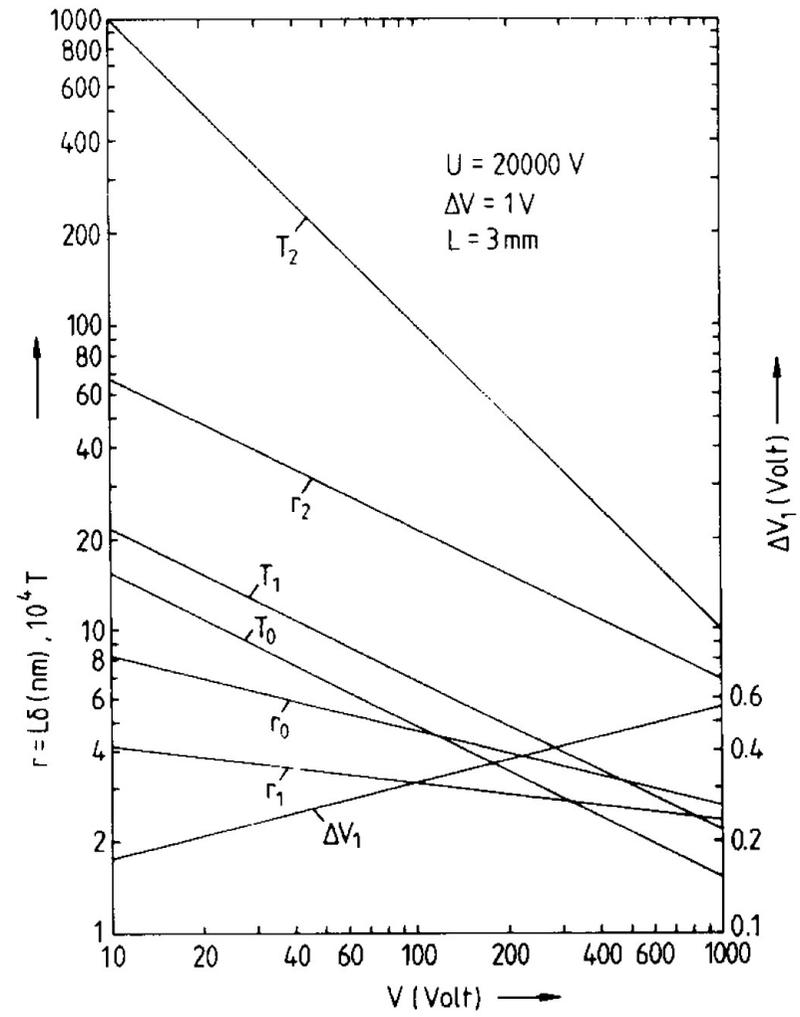
In emission microscopy (wide α range) optimum resolution condition reduces transmission T , therefore

optimize T^n/d^2 instead of $1/d^2$

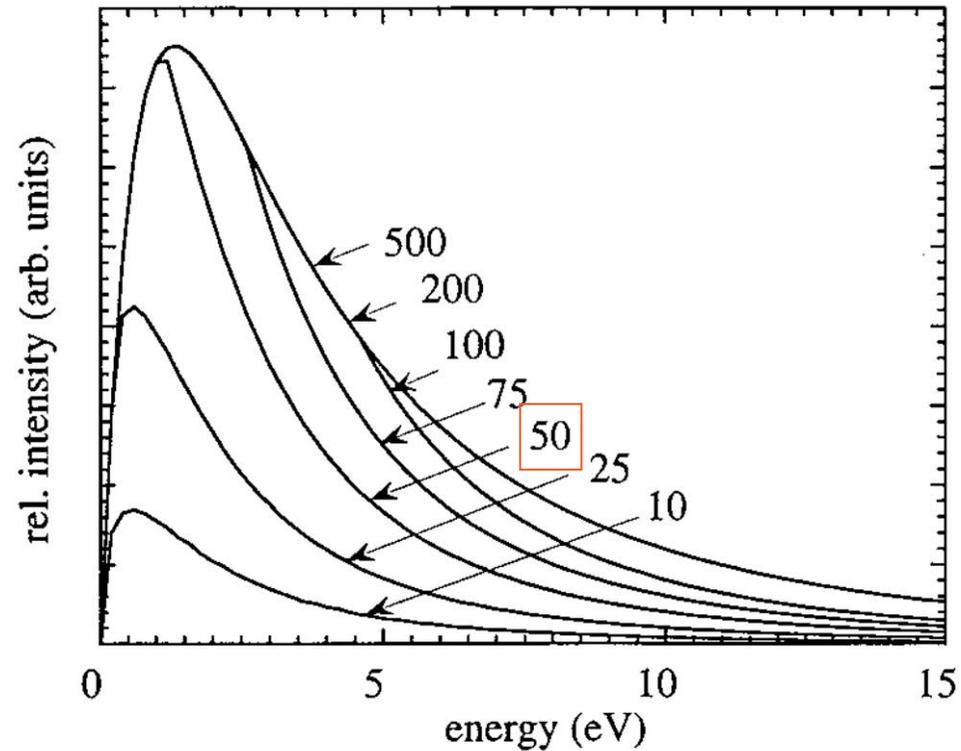
For $\cos \alpha$ distribution $T = \pi \sin^2 \alpha$

$$T^n/d^2 = \pi \sin^{2n}/d^2$$

Transmission T_n , resolution r_n of homogeneous field



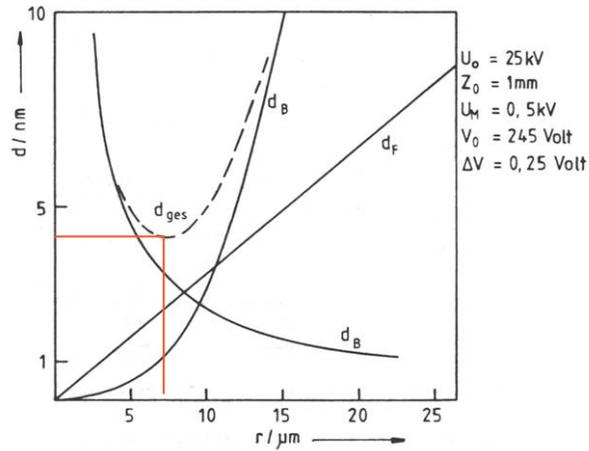
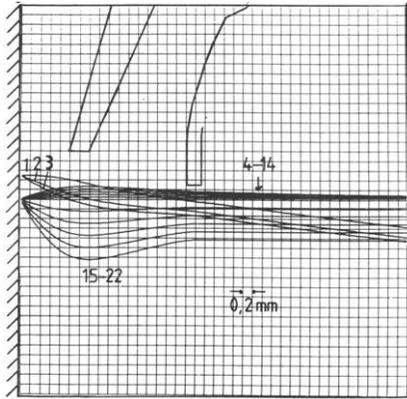
Influence of angle-limiting aperture on the energy distribution of secondary electrons



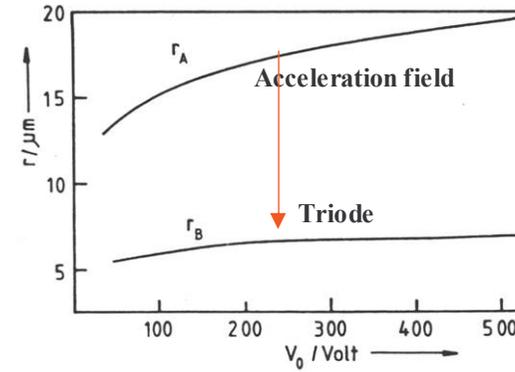
Work function $\Phi = 4$ eV, accelerating voltage $V = 20$ kV
Parameter: aperture diameter in μm , ALS PEEM

Real lenses

Acceleration and imaging fields combined Electrostatic triode

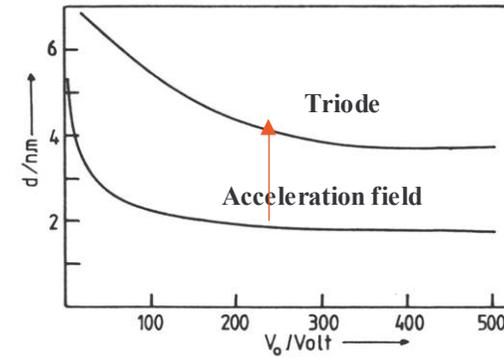


Optimum aperture



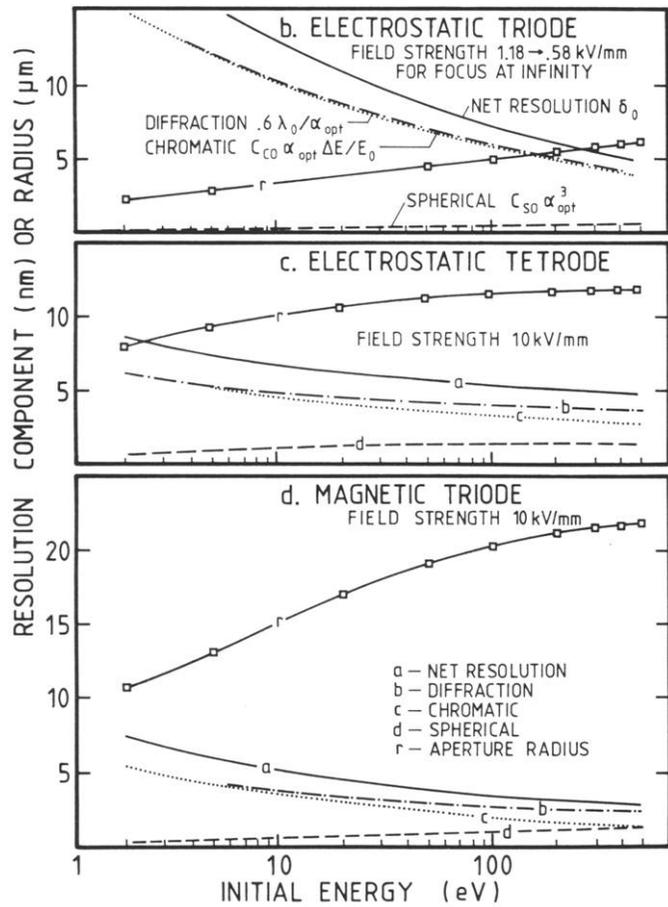
1,3: z_F, f, z_I
 1,2 (ΔE): c_c
 15-22 ($\times 50$): c_s $\alpha_{\max} = 9^\circ$
 4-14 to scale $\alpha_{\max} = 80^\circ$

Resolution



Resolution and optimum aperture

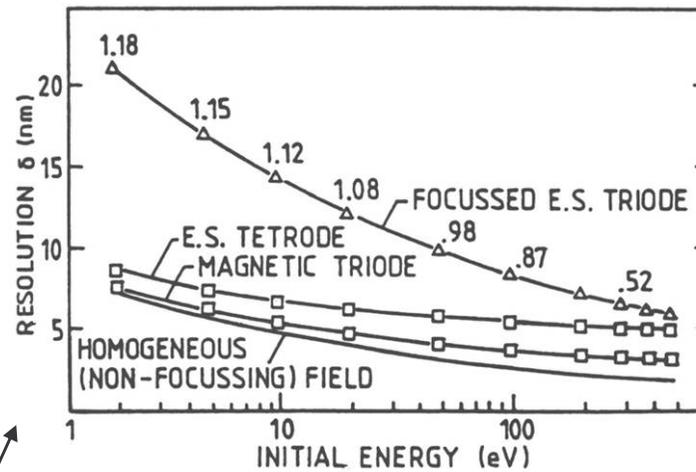
Optimum aperture r and resolution-limiting contributions



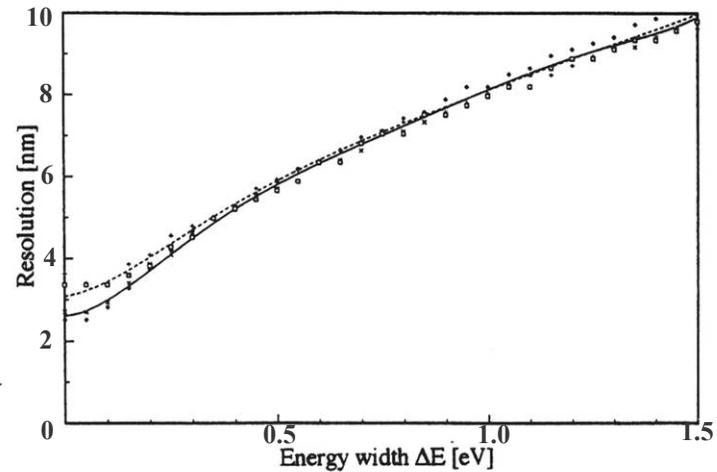
J. Chmelik et al, Optik 83 (1989)155

T. Müller, M.S. thesis, TU Clausthal 1995

**Resolution with optimum aperture
E-dependence at fixed $\Delta E = 0.5$ eV, $U_0 = 20$ keV**



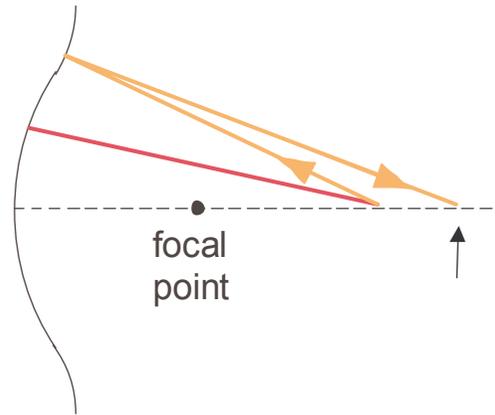
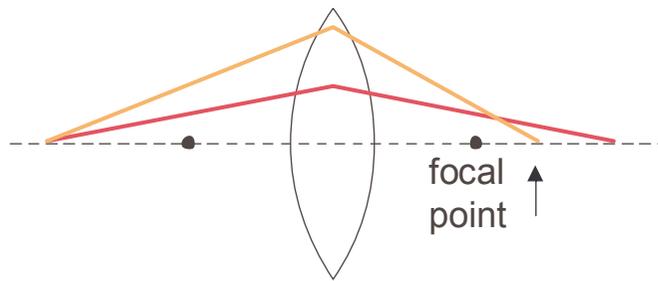
**ΔE -dependence at fixed $E = 10$ eV, $U_0 = 18$ kV
magnetic triode**



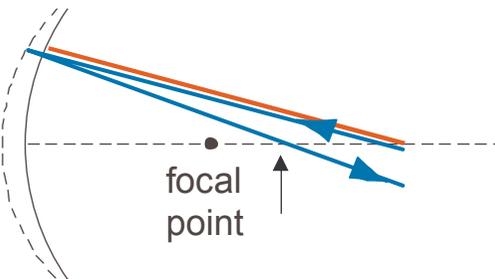
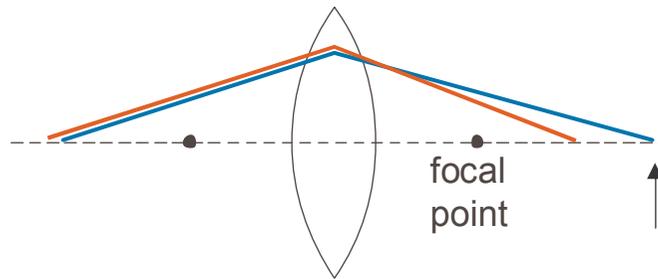
Aberration correction in electron optics

Round **convex** lenses

electrostatic mirror



Spherical aberration

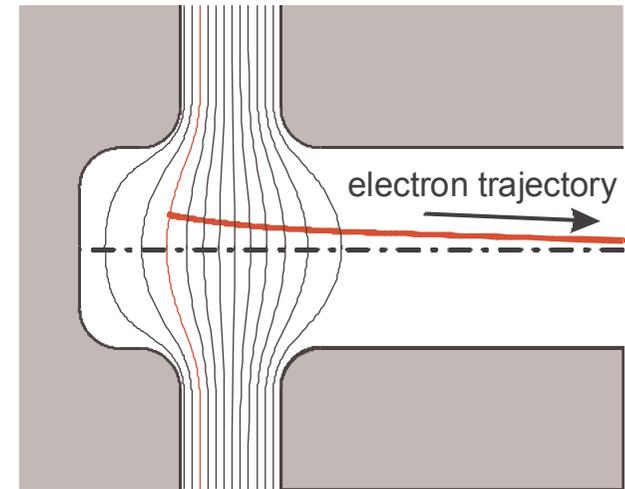


Chromatic aberration

Equipotential surfaces
in a diode mirror

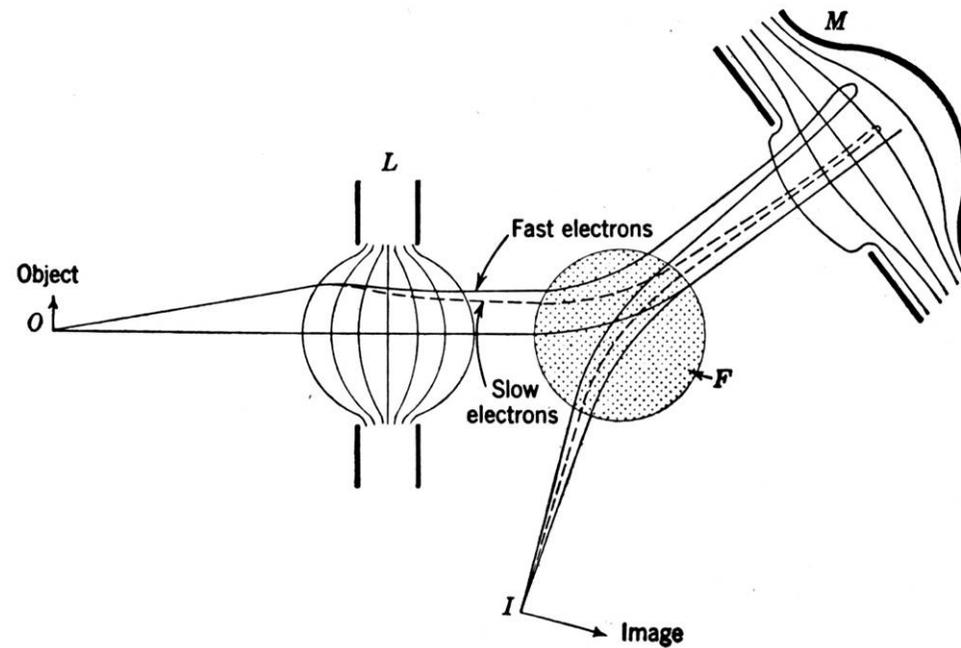
outer electrode
at -3750 V

inner electrode
at 15000 V



Resolution improvement by aberration correction

with electron mirror

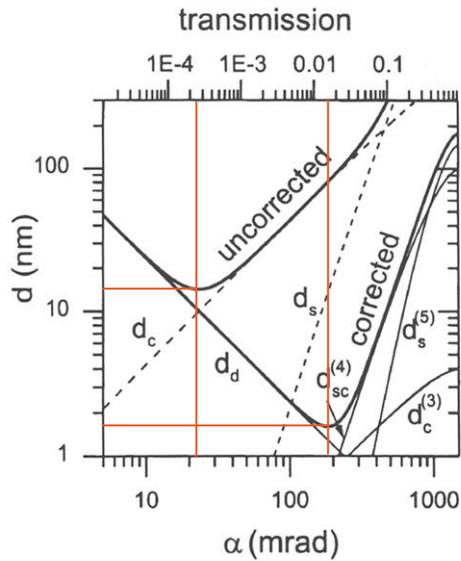


V.K. Zworykin et al, *Electron Optics and the Electron Microscope*, John Wiley, New York 1945

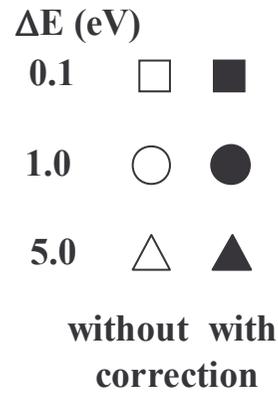
Recknagel 1935

Resolution and transmission improvement with aberration correction

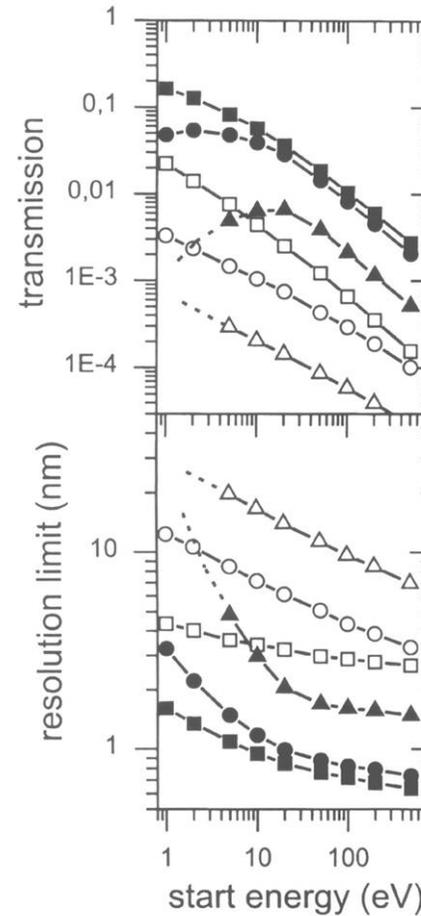
Example: SMART



$E_0 = 10$ eV, $\Delta E = 2$ eV, $F = 5$ kV/mm

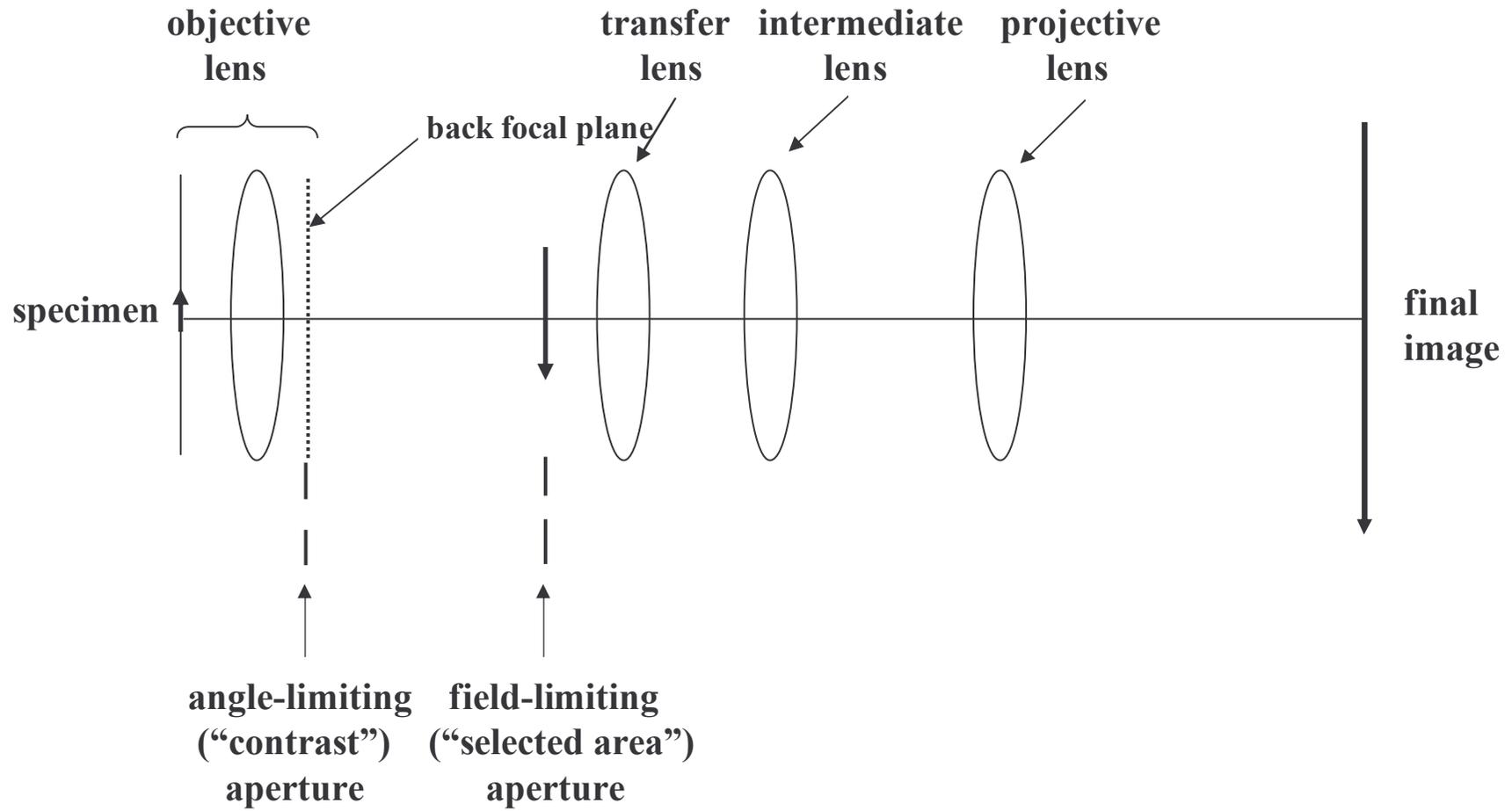


Calculations: D. Preikszas
From Th. Schmidt et al,
Surf. Rev. Lett. 9 (2002) 223

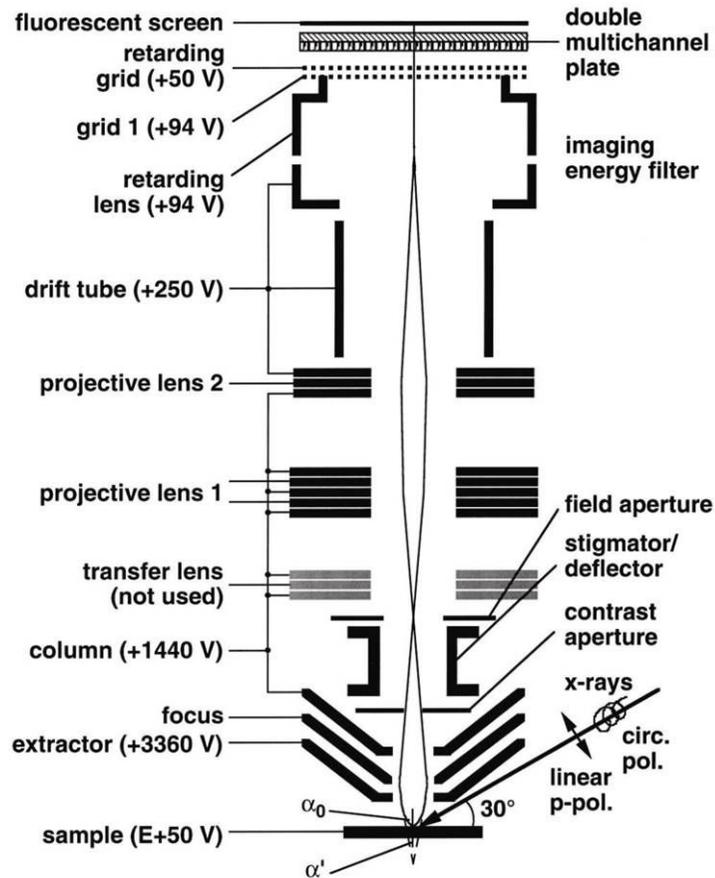


Instruments

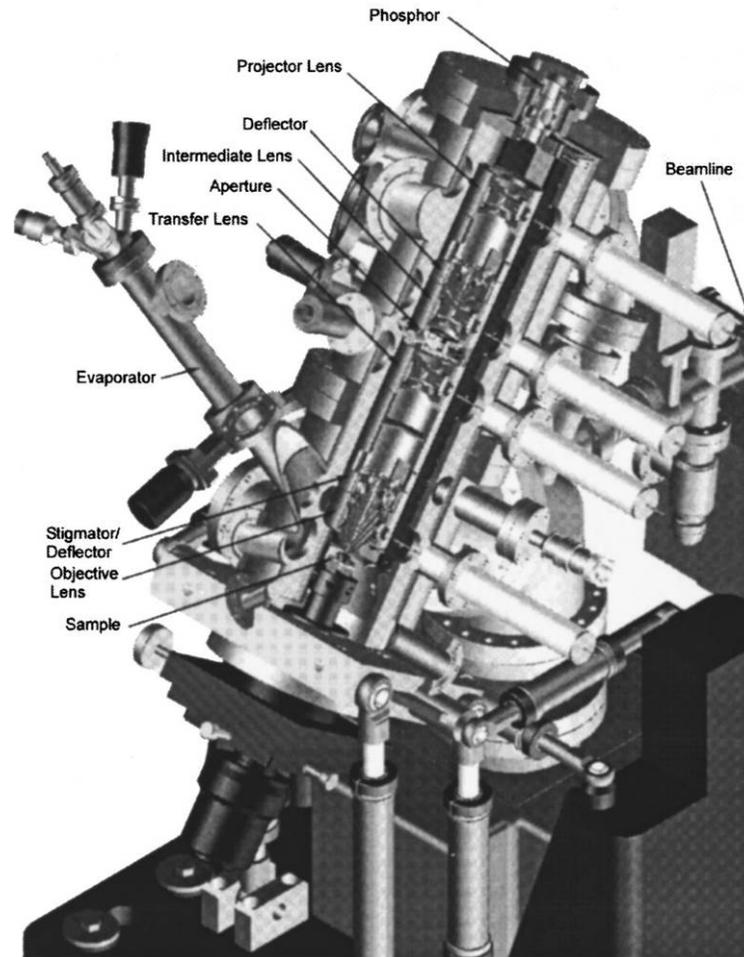
Basic PEEM schematic



Electrostatic PEEM examples

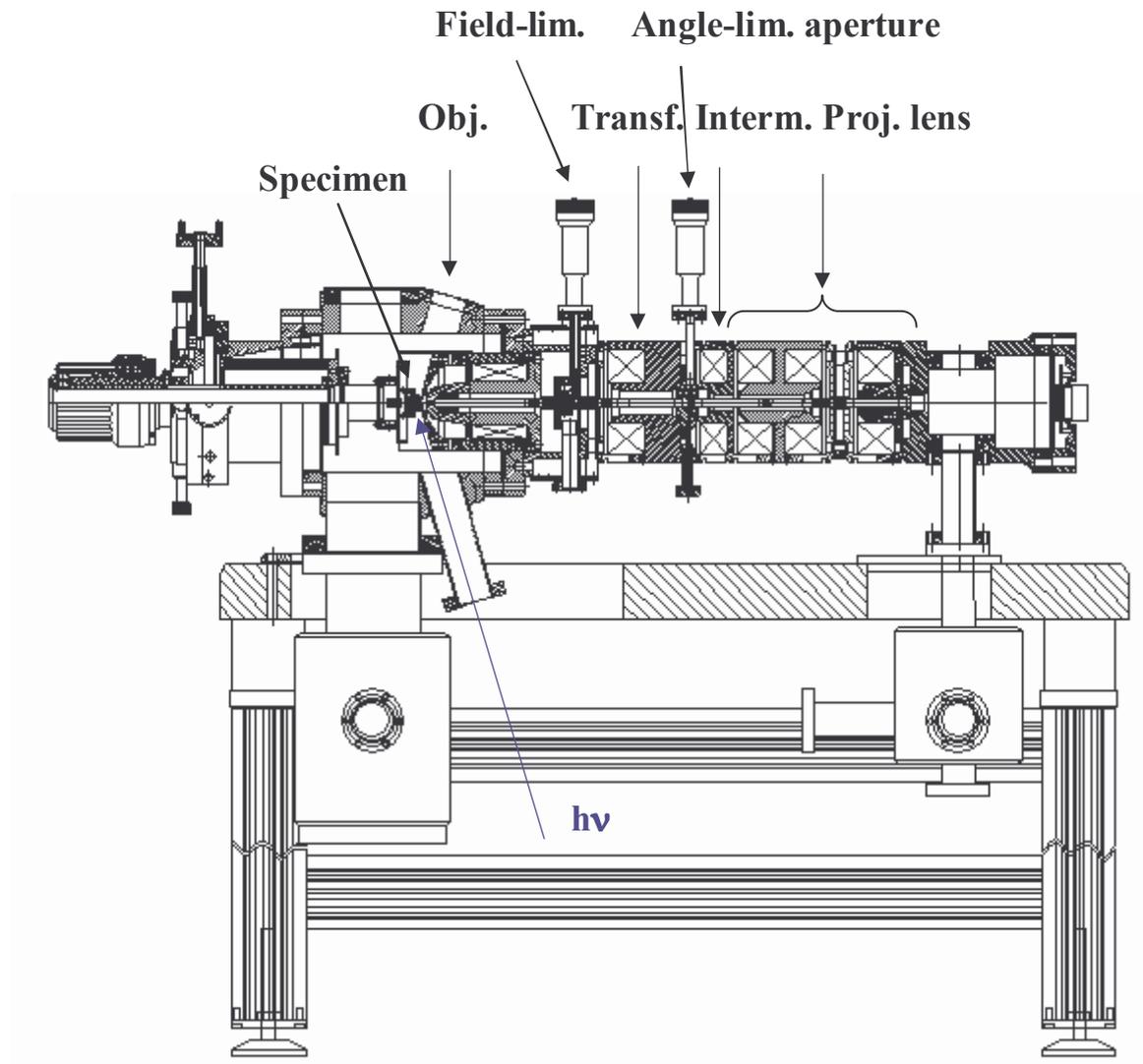


**Focus PEEM
with high pass filter**



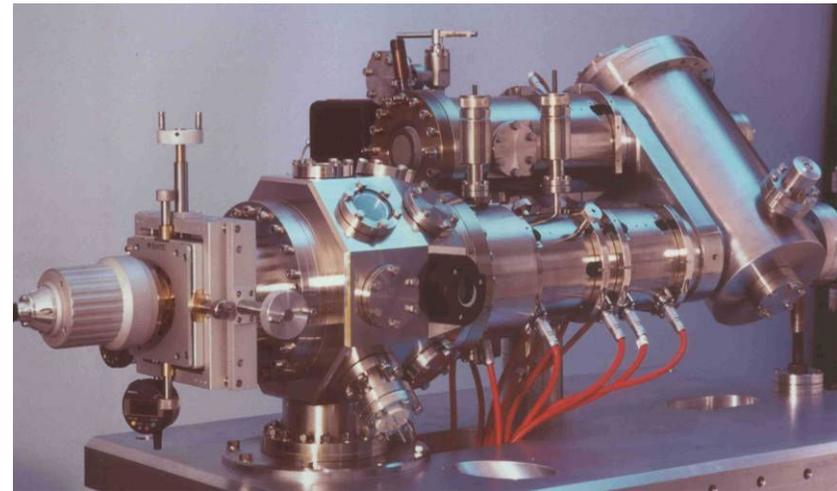
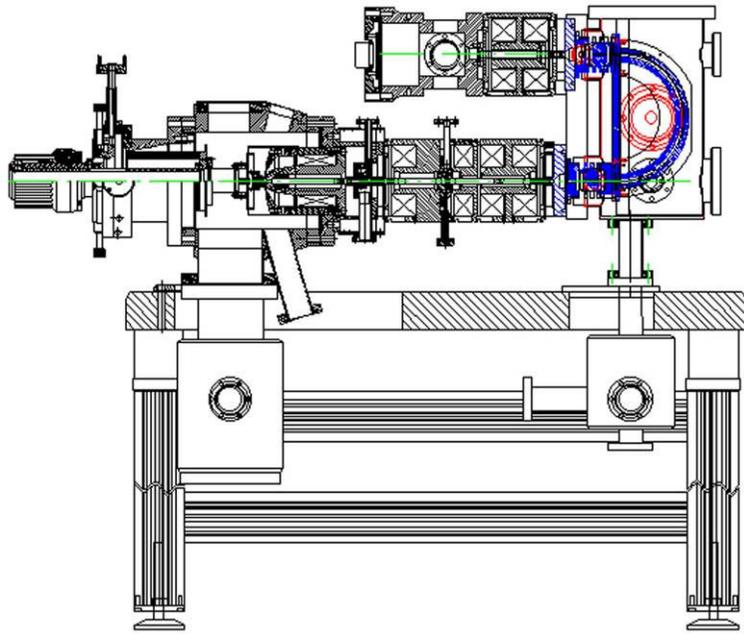
ALS PEEM II

Magnetic PEEM (ELMITEC)



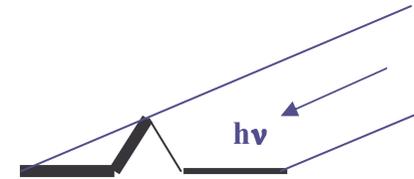
Spectroscopic PEEM with band pass filter

ELMITEC



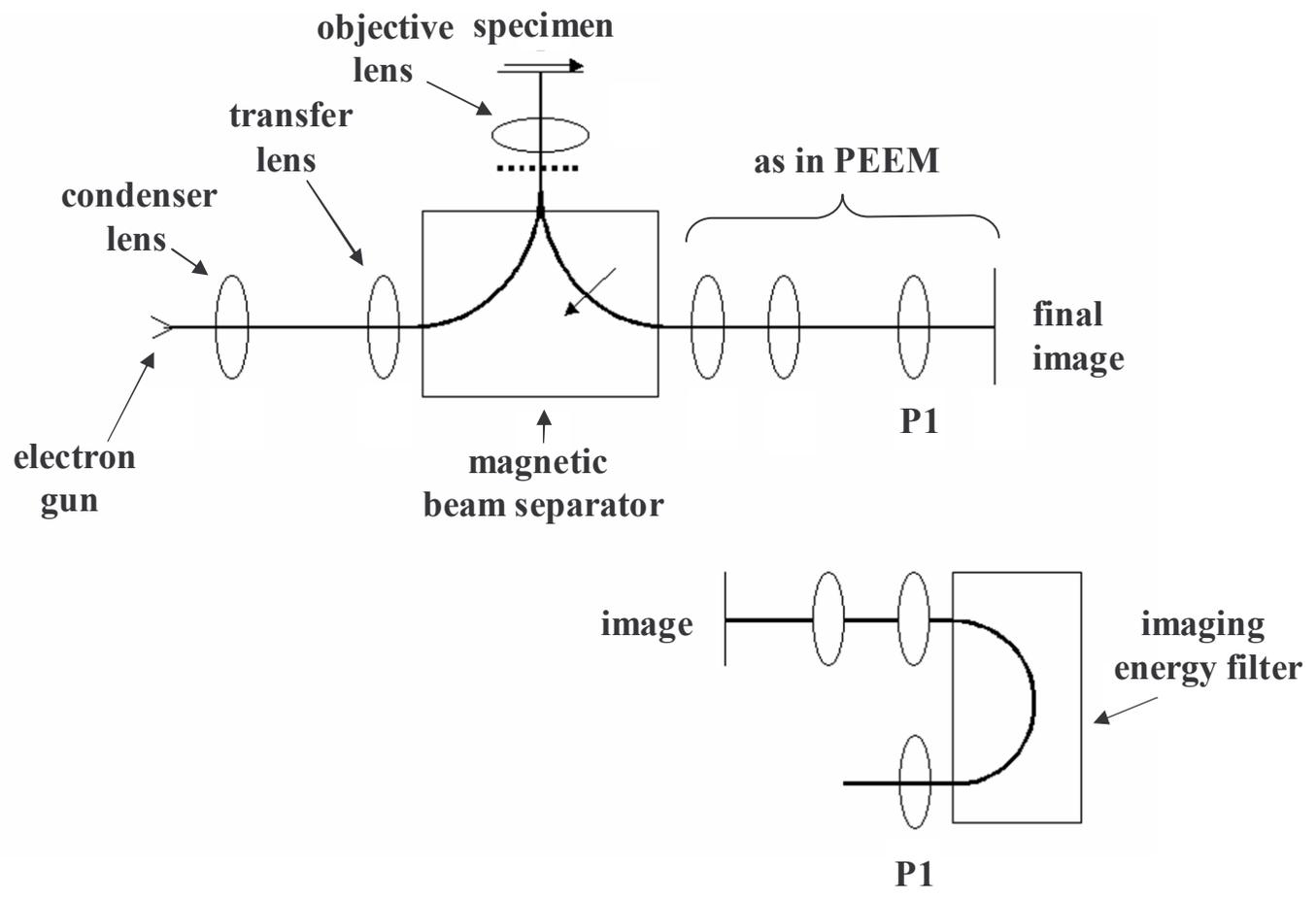
Contrast mechanisms

- 1 Topographic contrast due to oblique illumination and field distortion
- 2 Work function contrast at low E_0 (escape probability!)
- 3 Chemical contrast due to inner shell ionization
- 4 Magnetic contrast via XMCD and XMLD



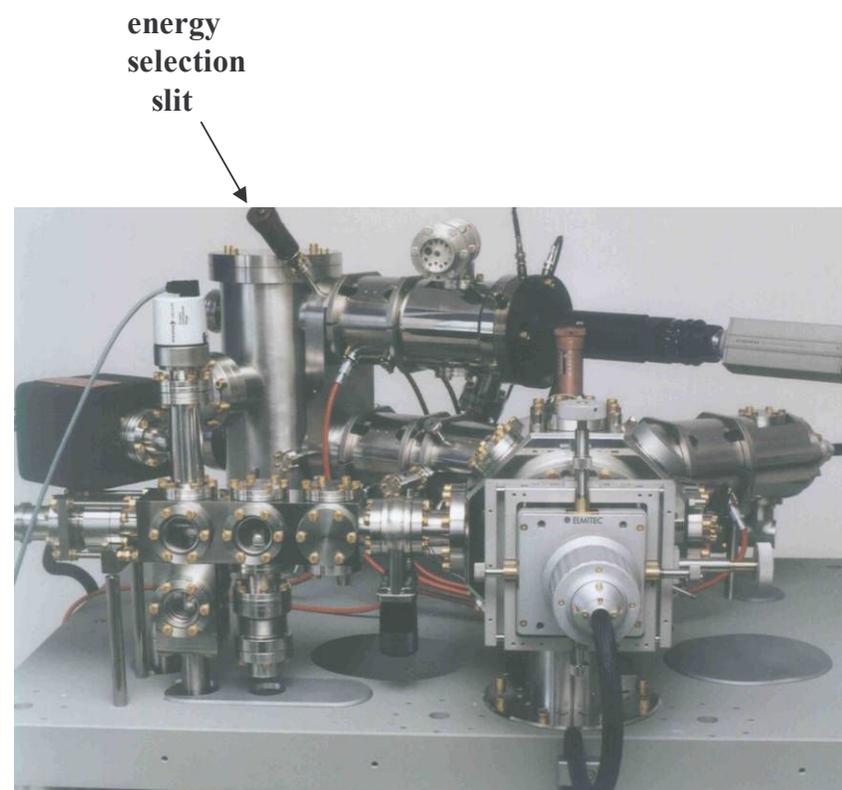
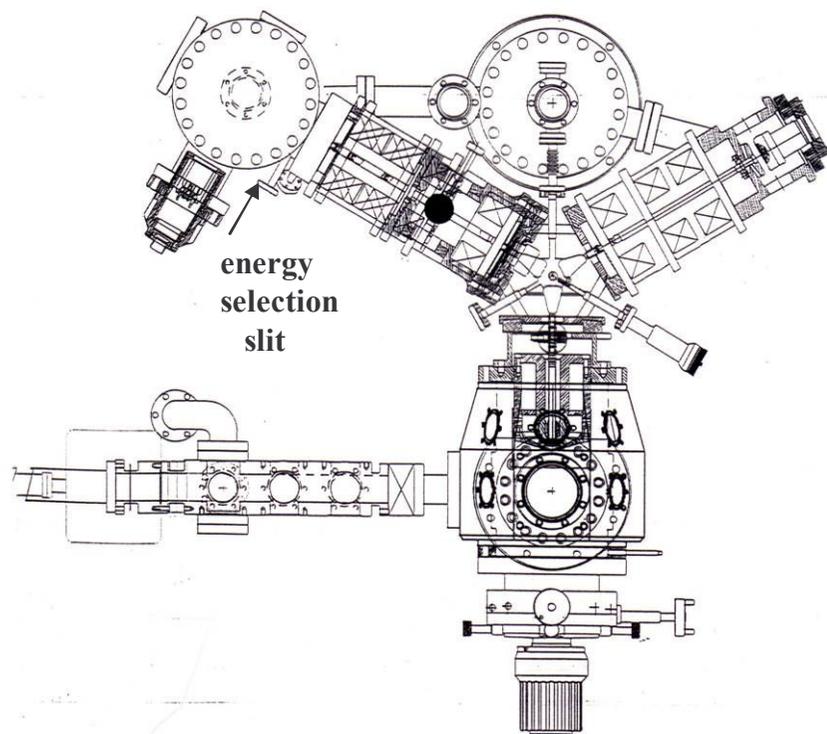
No structural contrast, therefore combination with
Low Energy Electron Microscopy
(LEEM)

Basic LEEM schematic



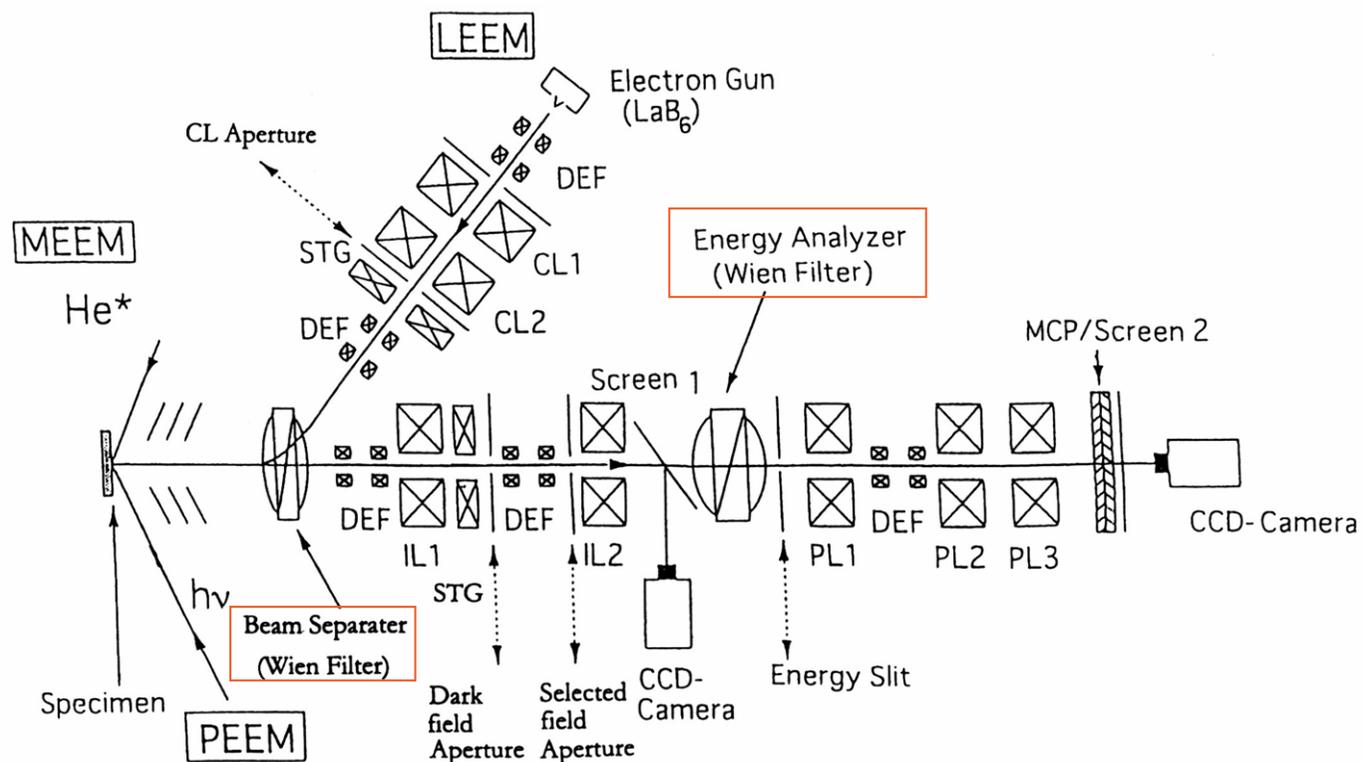
Spectroscopic Photo Emission and Low Energy Electron Microscope

SPELEEM ELMITEC



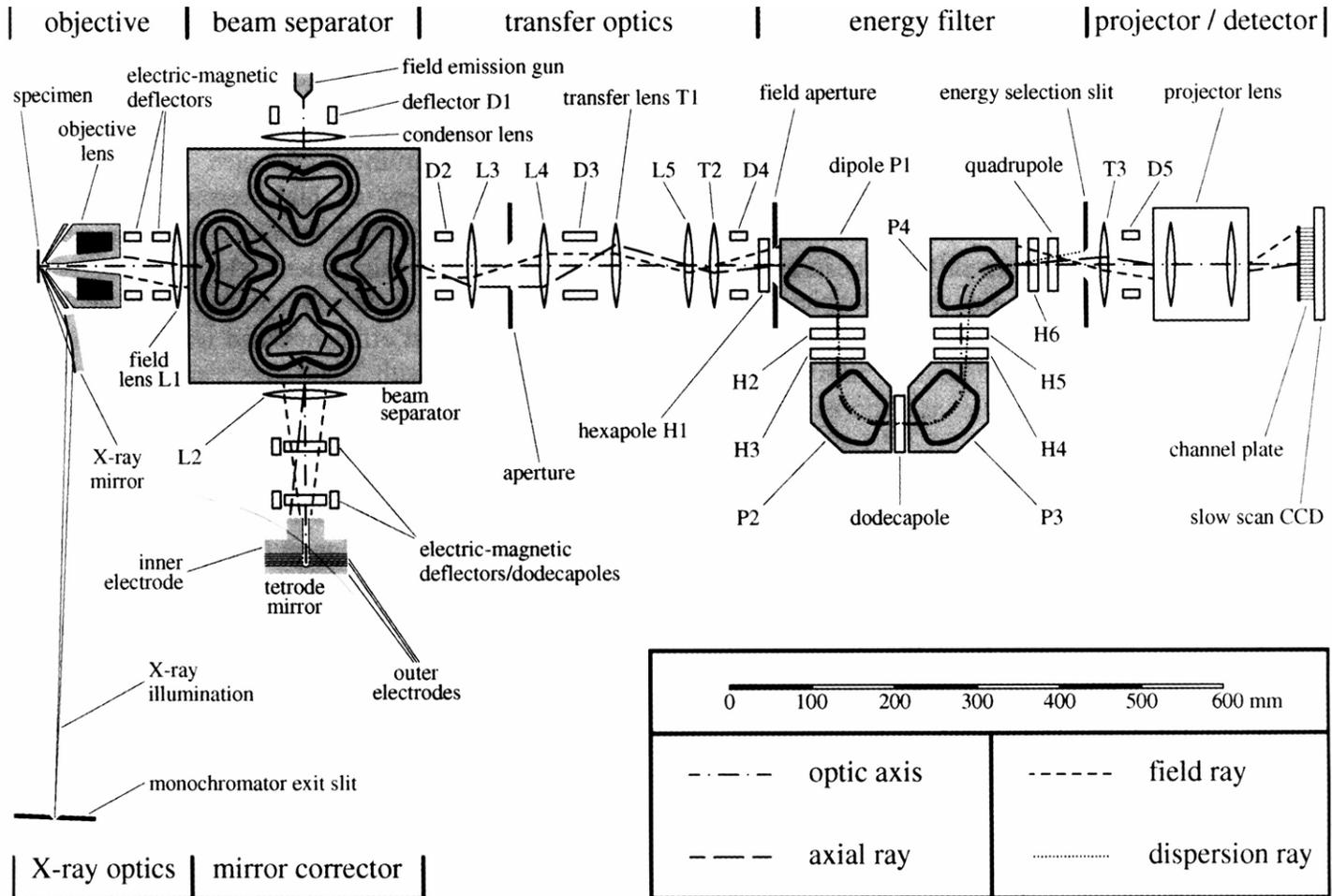
LEEM with energy filter

JEOL



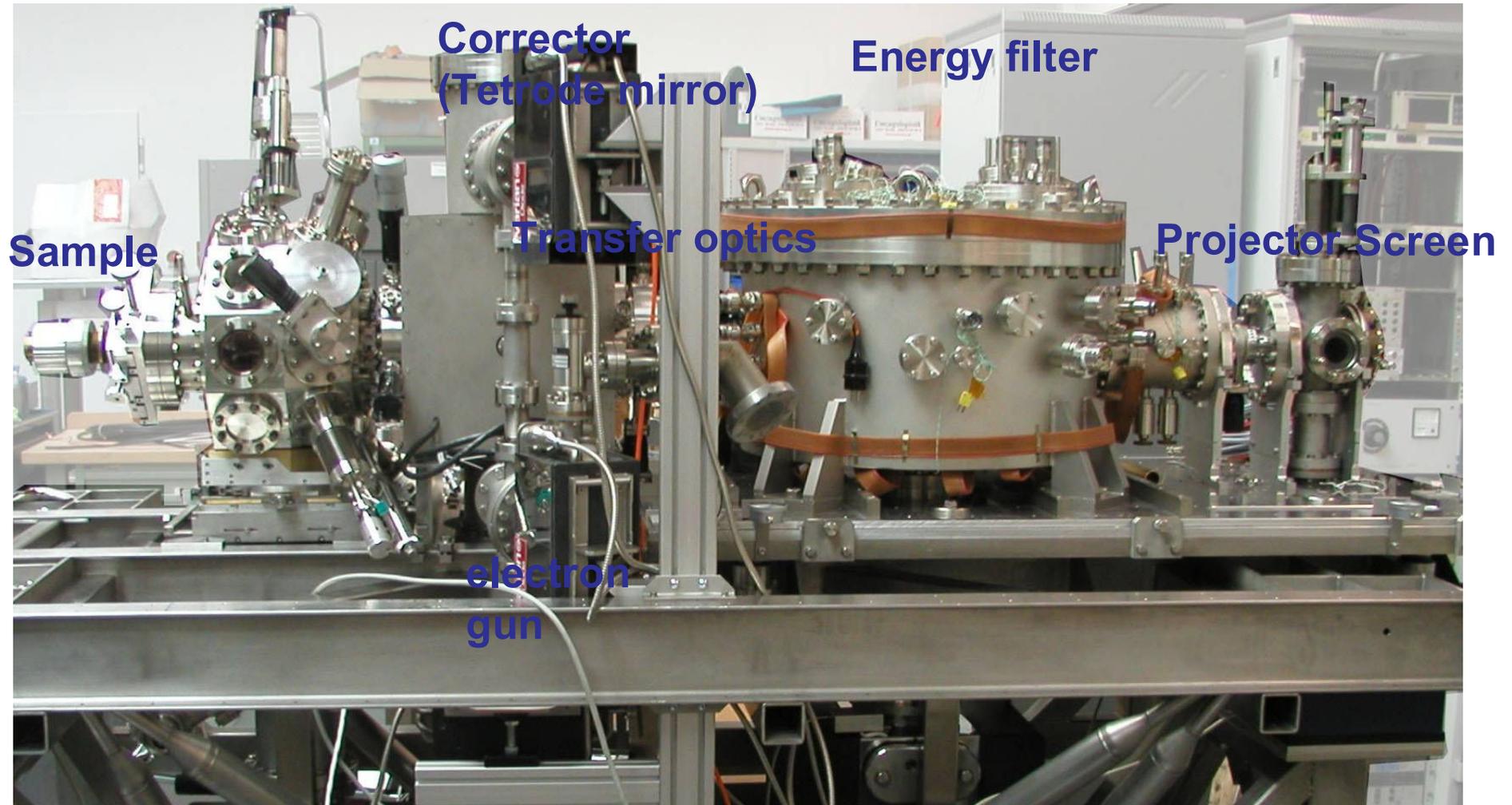
Aberration-corrected SPELEEM

SMART (BESSY II)



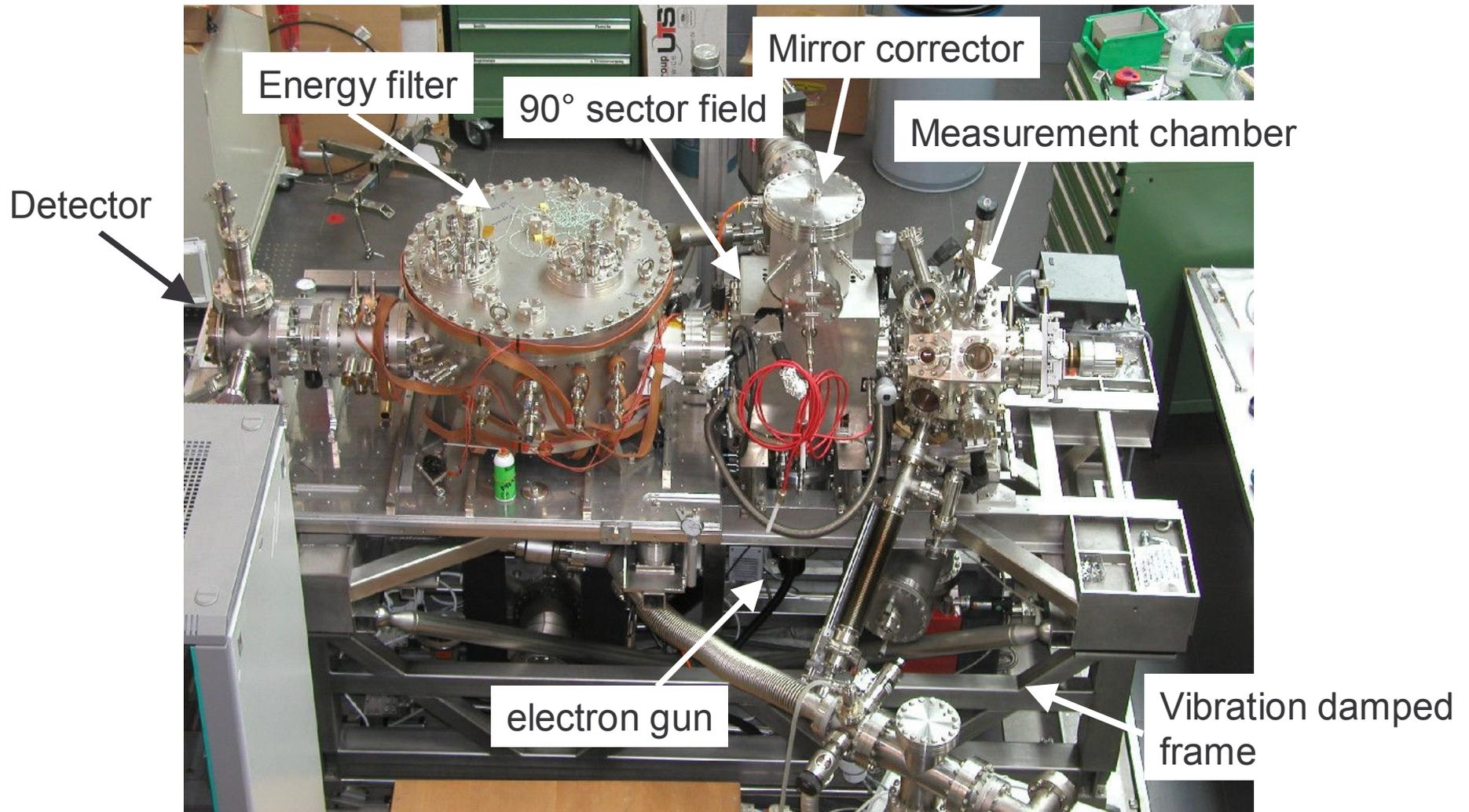
SMART side view

Aberration corrected PEEM/LEEM with energy filtering



Th. Schmidt April 2004

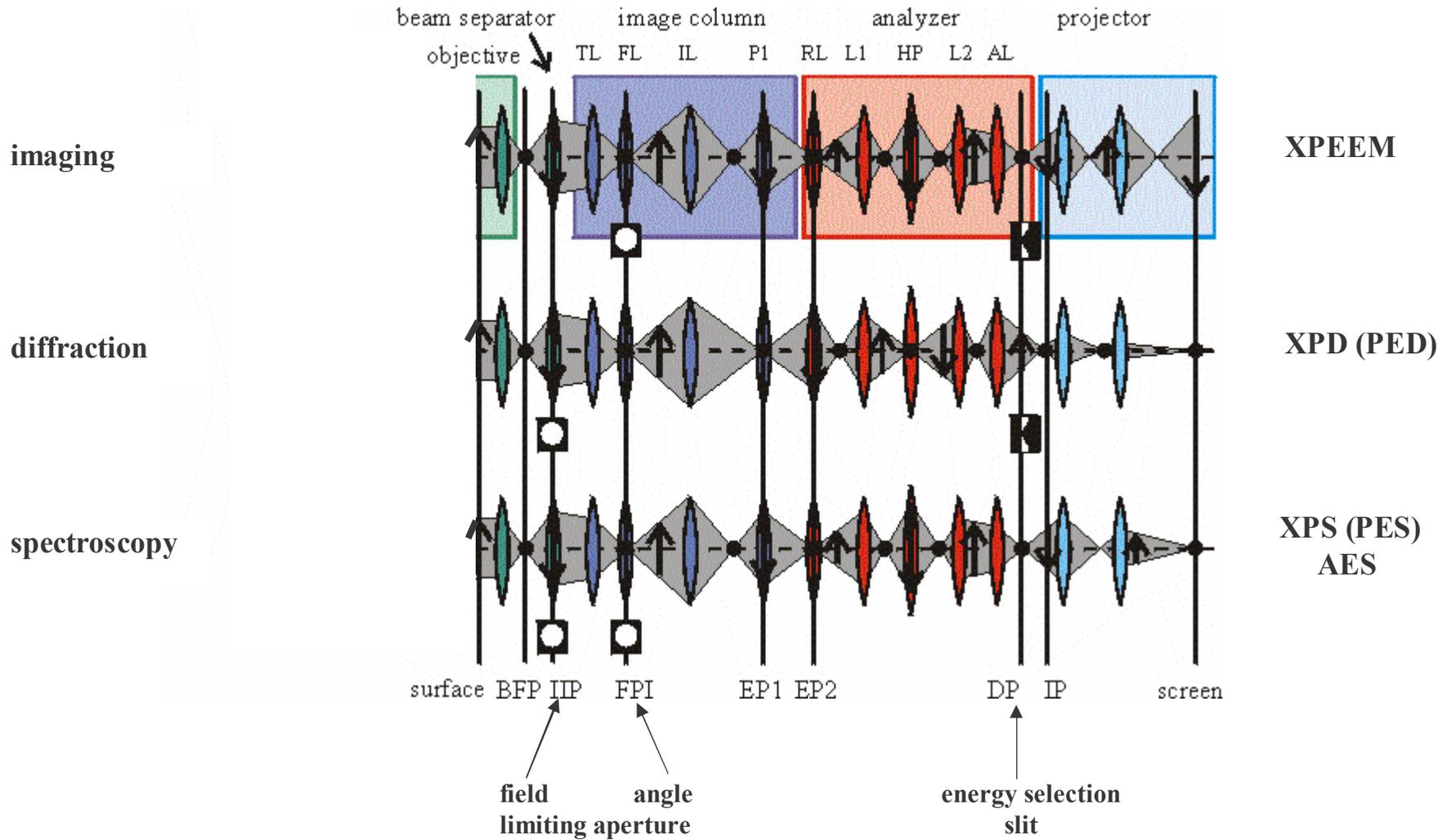
SMART top view



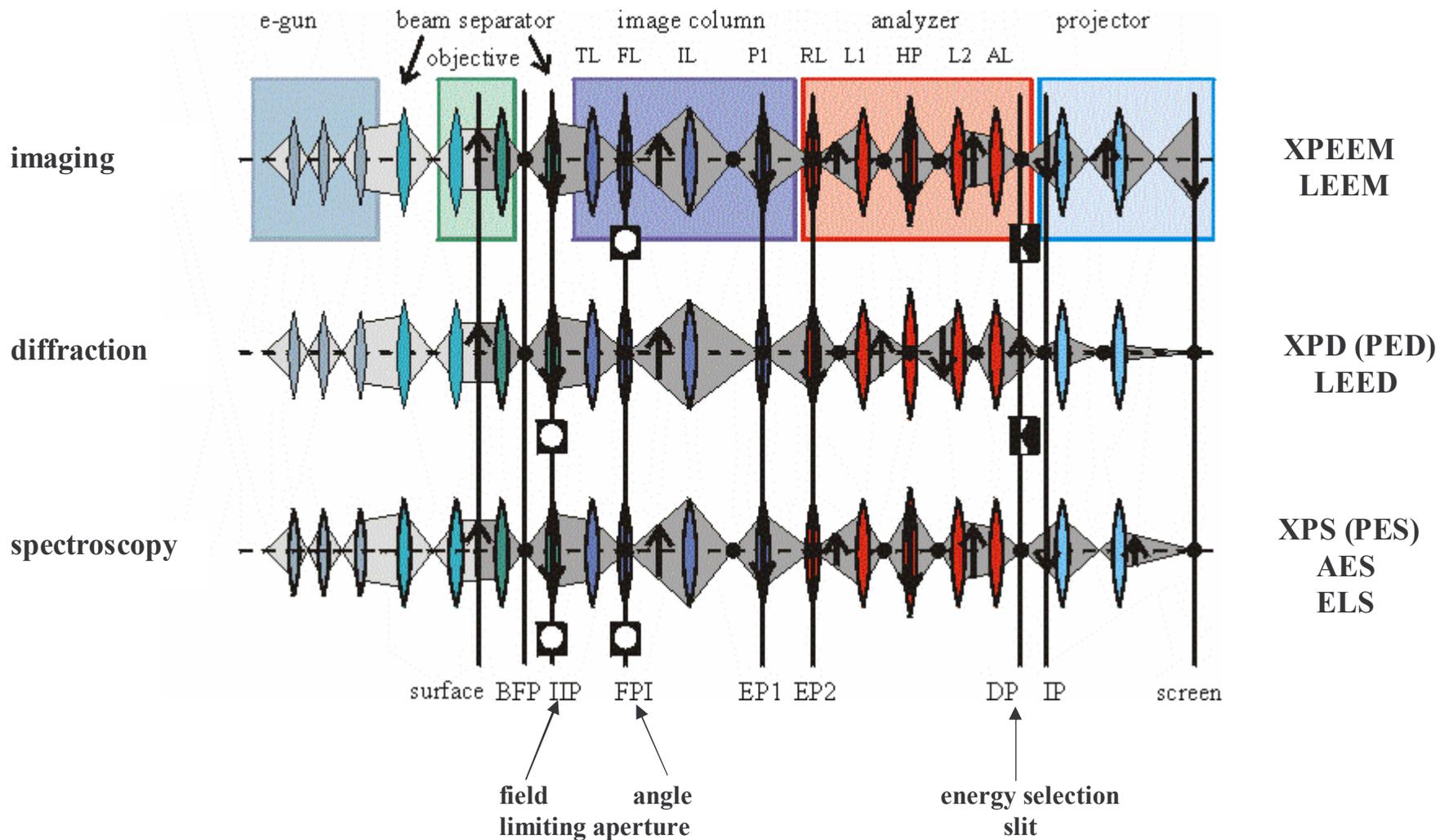
Th. Schmidt April 2004

Methodic

Operation modes of a SPELEEM



Operation modes of a SPELEEM



PEEM practice

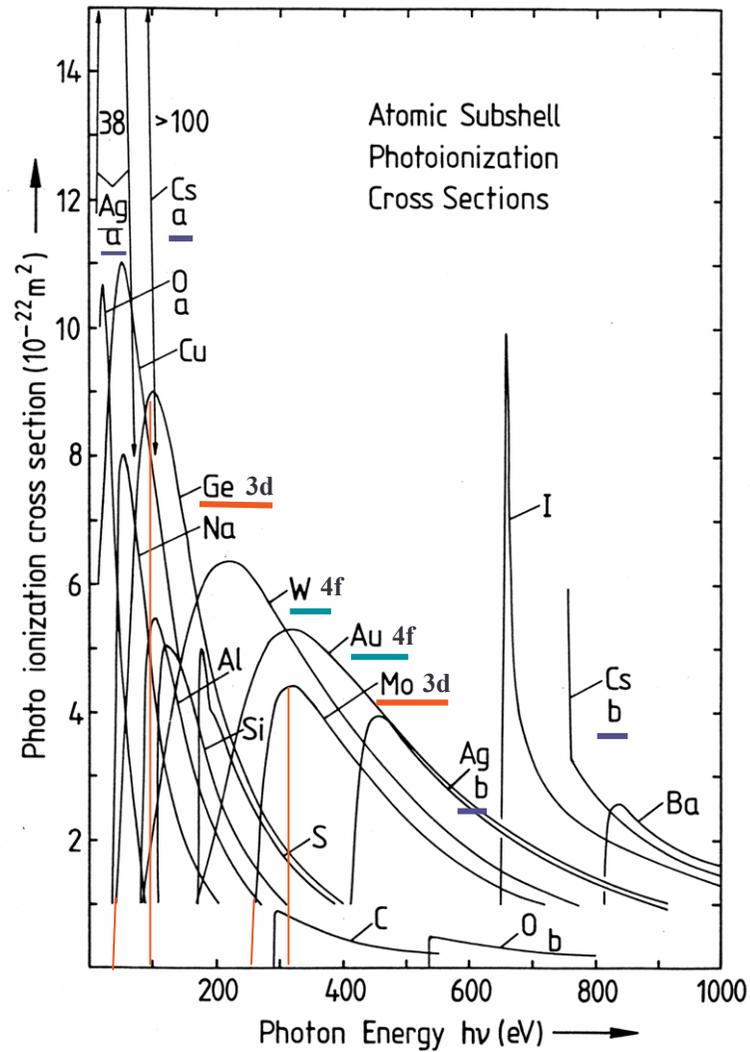
- 1 **Ultrahigh vacuum (low 10^{-10} torr range)**
but experiments up to 10^{-5} torr range possible
- 2 **Surface cleaning: heating, sputtering or chemical reactions, e.g with oxygen for carbon removal**
- 3 **Choice of optimum photon energy:**
 - a. **Secondary electron imaging: $h\nu \approx E_i$ (XANES, NEXAFS, XMCD, XMLD)**
 - b. **Photo electron imaging: $E_i + 30 \text{ eV} < h\nu < E_i + 100 \text{ eV}$**

to minimize
secondary electron
background

to maximize
transmission
and
photo electron yield

Photo ionization cross sections

Photon energy selection



Binding energies (eV)

Ge 3d 29.8, 29.2

Mo 3d 231.1, 227.9

W 4f 33.6, 31.4

Au 4f 87.6, 84.0

Ag

a 4d ≈ 5

b 3d 374.0, 368.3

Cs

a 4d 79.8, 77.5

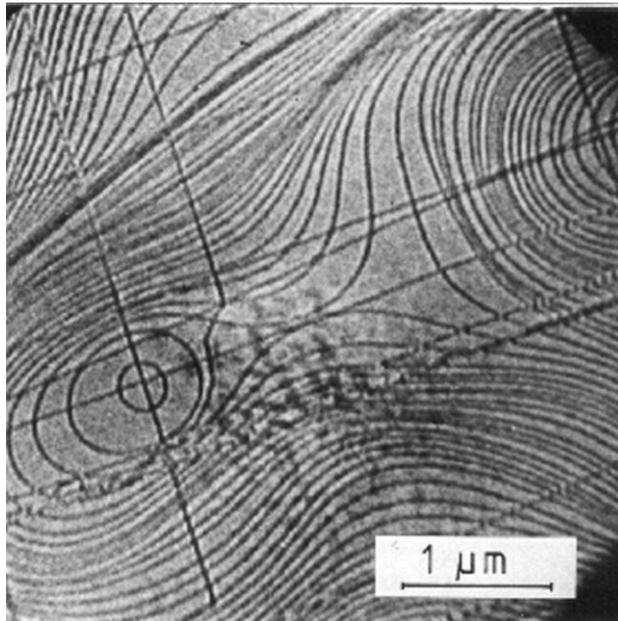
b 3d 740.5, 726.6

J.J. Yeh and I. Lindau,
Atomic Data 1985

The usefulness of LEEM

Properties not visible with PEEM, but with LEEM

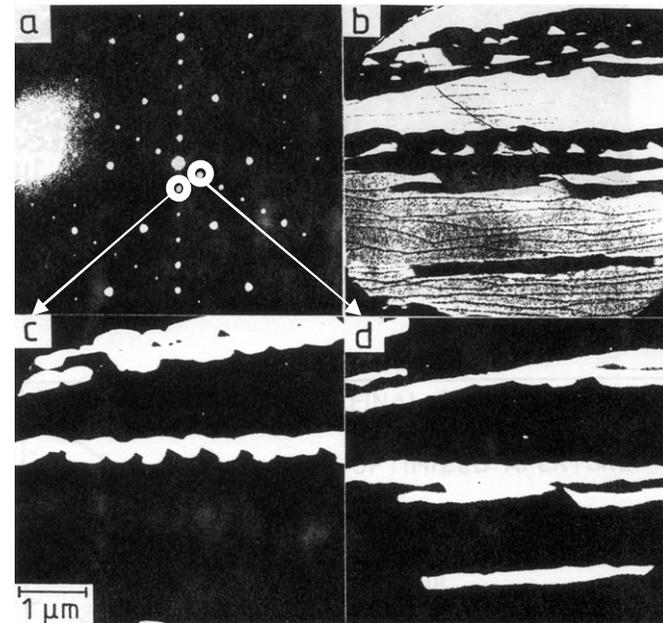
atomic steps



Mo(110)

interference contrast

domain orientations



Au($\sqrt{3} \times \sqrt{3}$)-R30° + Au(5 × 2) on Si(111)

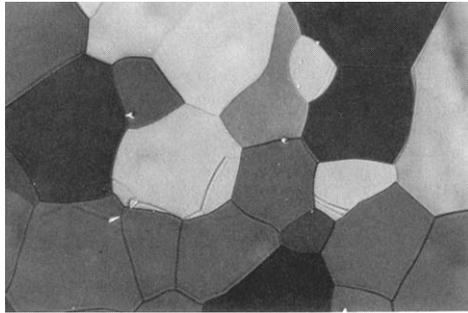
b c,d
diffraction contrast

LEEM also much brighter and better resolution ⇒ use for focusing in XPEEM

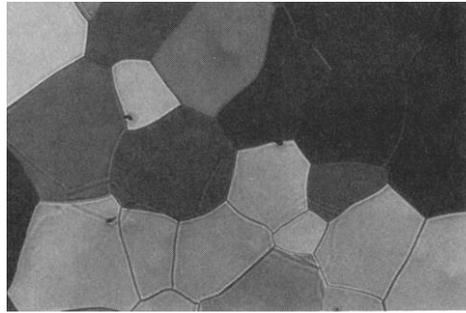
LEED much easier to interpret than PED ⇒ use for structure analysis

Classical emission microscopy

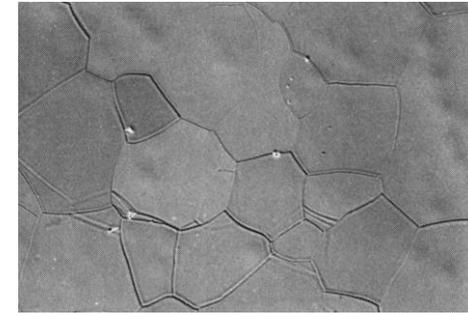
Polycrystalline tantalum



thermionic emission



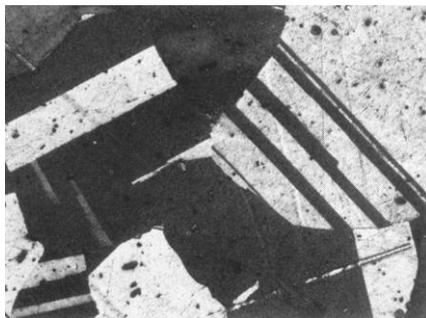
threshold photo emission



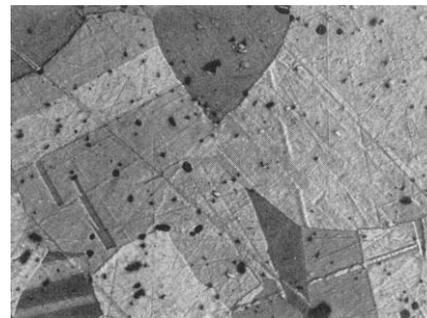
secondary emission

20 μm

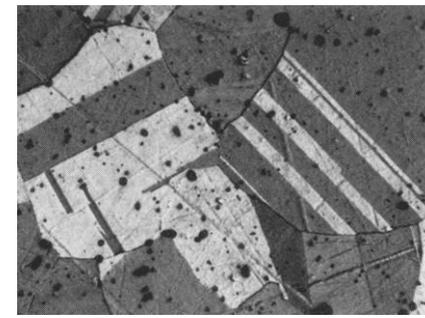
Photo emission from polycrystalline beryllium bronze



low



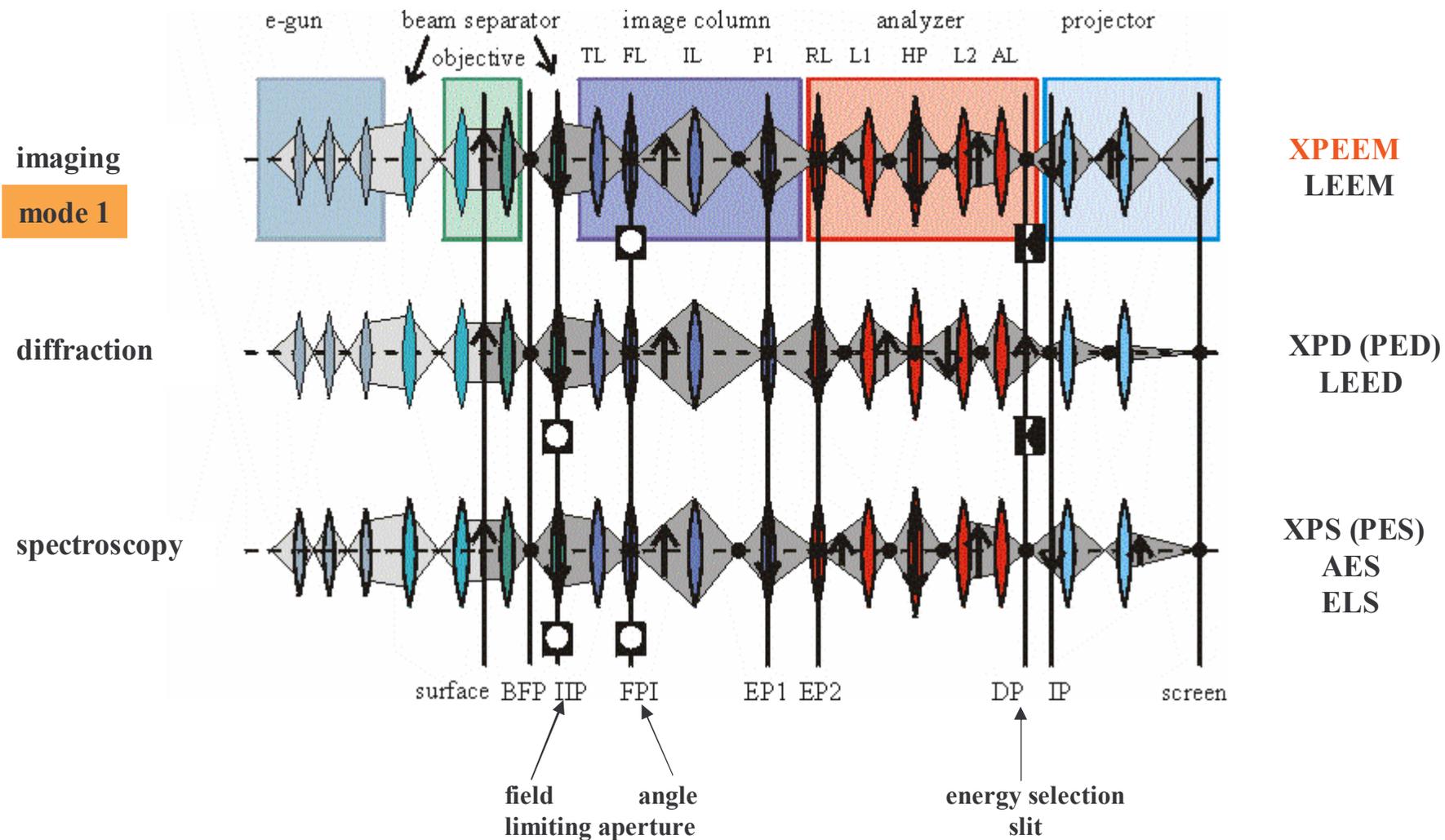
10 μm
medium



high

energy region of the UV spectrum of a Hg high pressure lamp

Operation modes of a SPELEEM



Chemical imaging (mode 1)

secondary electrons
spatial resolution

$$\sigma_{\text{Ag}4d} \approx 5 \sigma_{\text{W}5d}$$

$$h\nu = 65 \text{ eV} \gg E_i < 10 \text{ eV}$$

$$\Delta E_F \leq 1 \text{ eV}$$

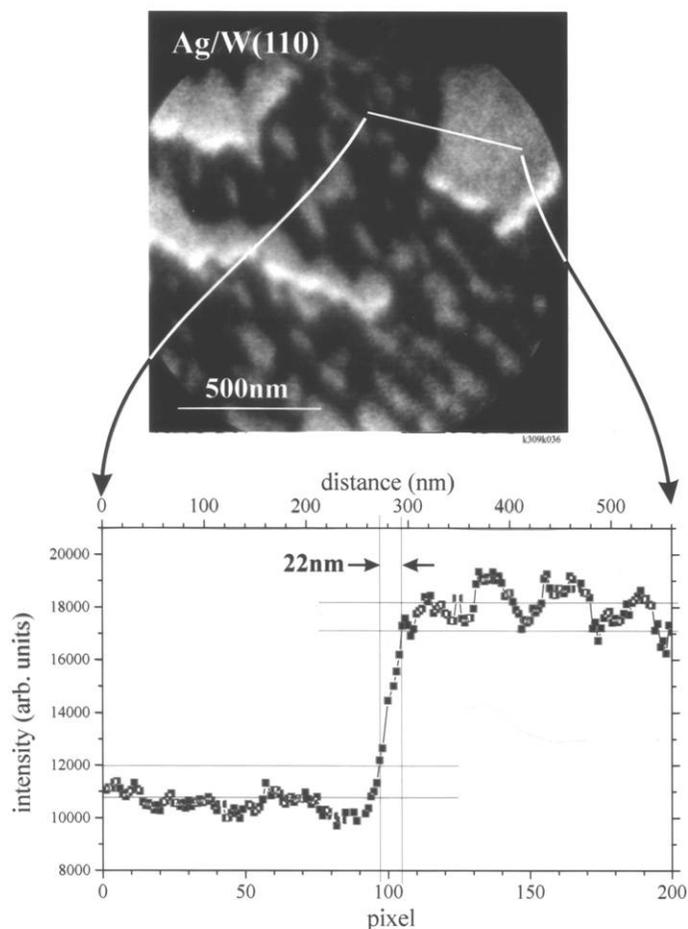
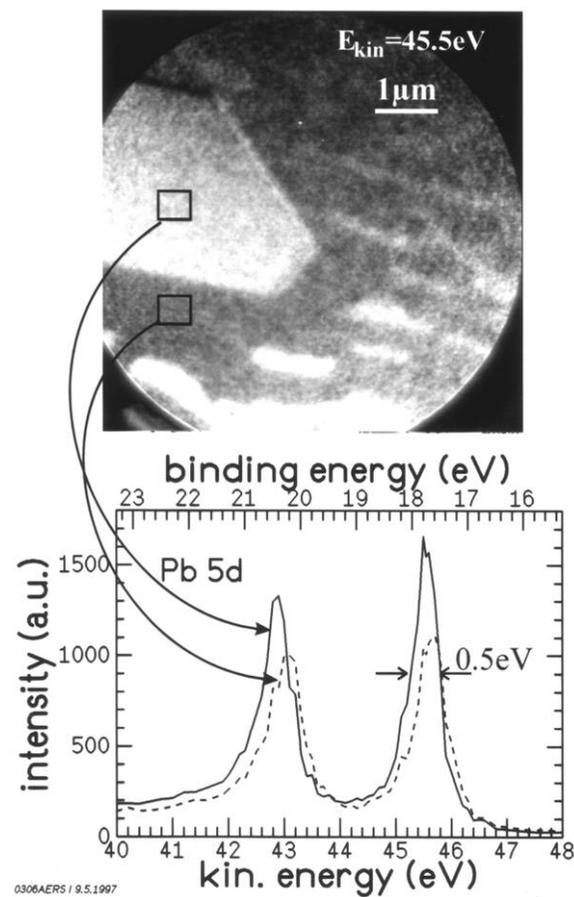


photo electrons
energy resolution

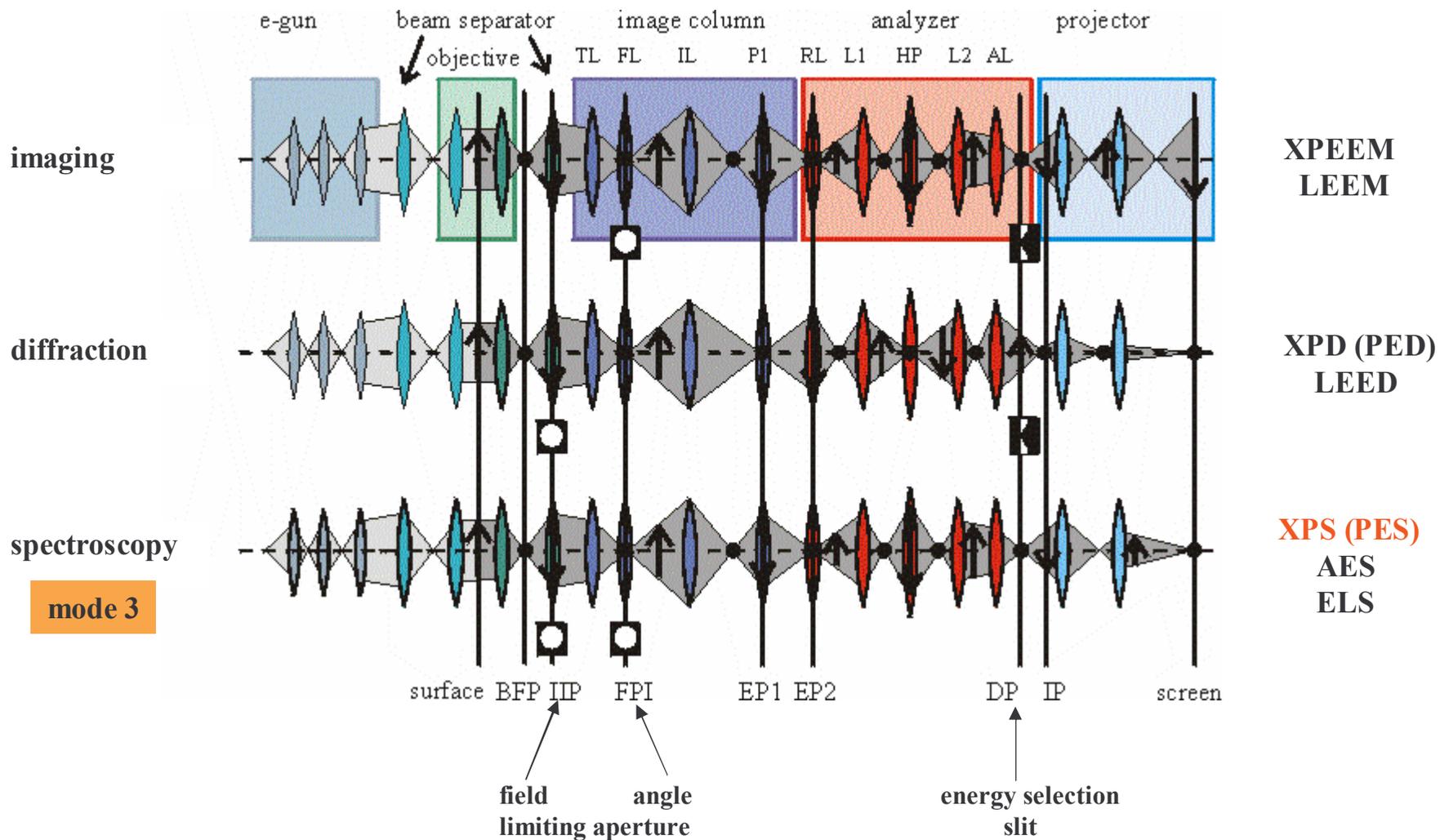
$$h\nu = 65 \text{ eV, images in } 0.2 \text{ eV steps}$$

$$10\text{-}60 \text{ sec/image } 0.25 \mu\text{m}^2 \text{ areas}$$

$$\Delta E_F \leq 0.5 \text{ eV, } \Delta E_{\text{chem}} \approx 0.15 \text{ eV}$$



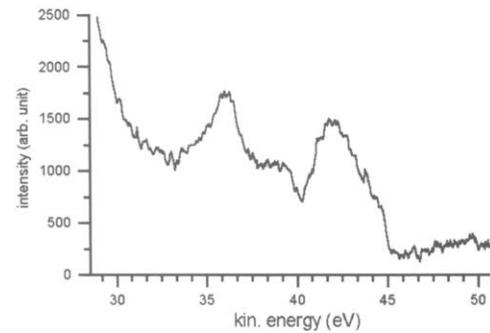
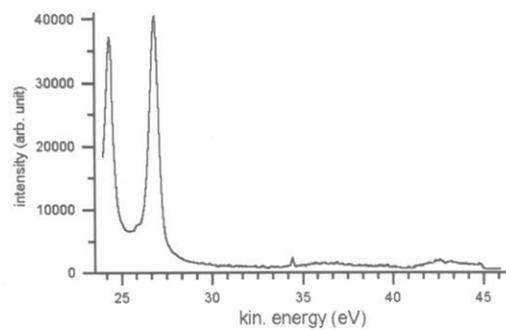
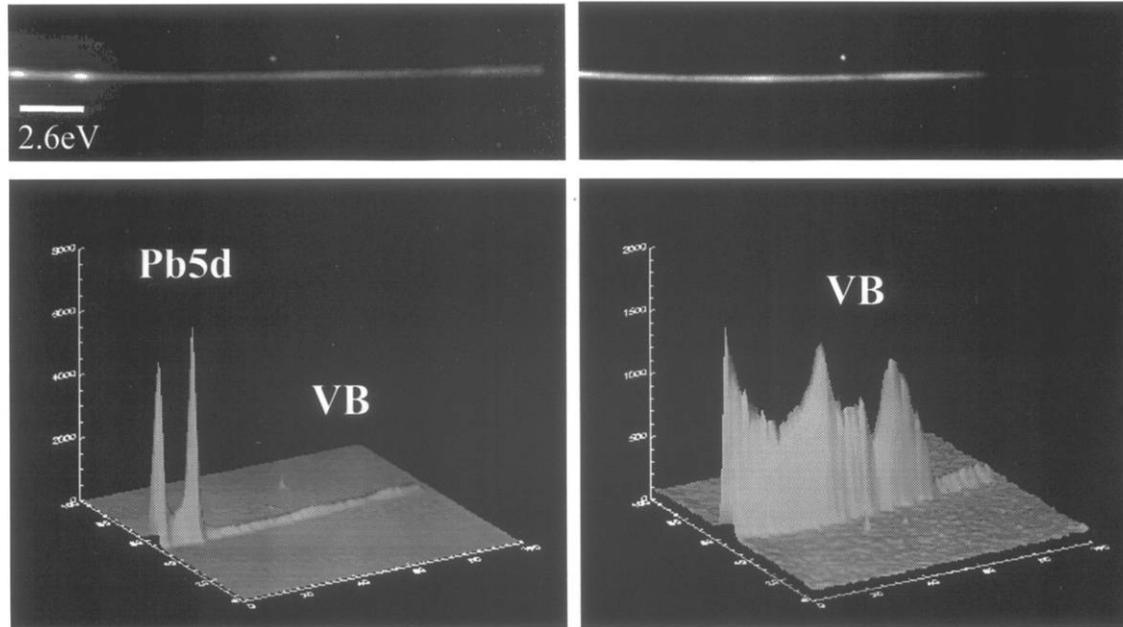
Operation modes of a SPELEEM



Fast local spectroscopy by imaging the dispersive plane (mode 3)

$\alpha = 8^\circ$ (contrast aperture), $0.8 \mu\text{m}^2$ area (selected field aperture)
20 eV full dispersion, 60 sec
 $h\nu = 48 \text{ eV}$

8 monolayers
Pb on Si(111)-
 $\sqrt{3} \times \sqrt{3}$ -Ag

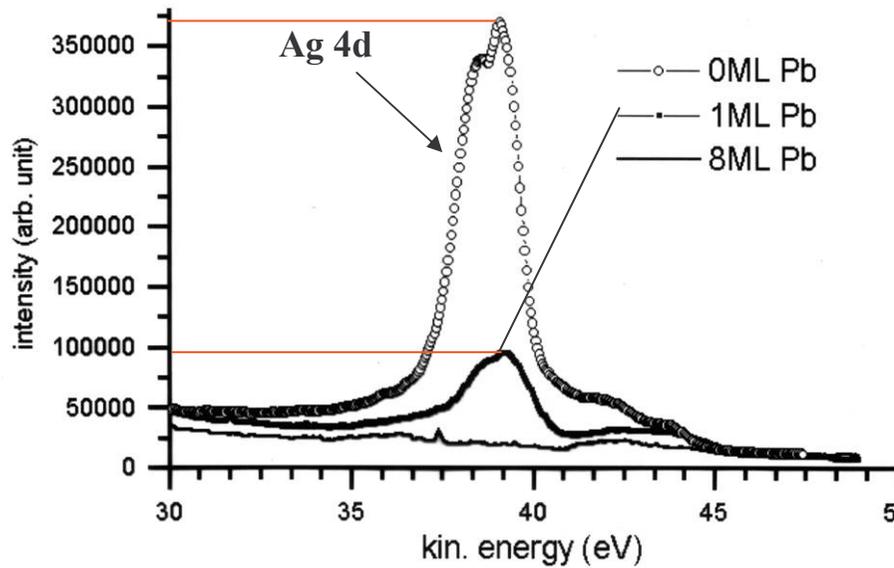


Surface sensitivity of photo electrons

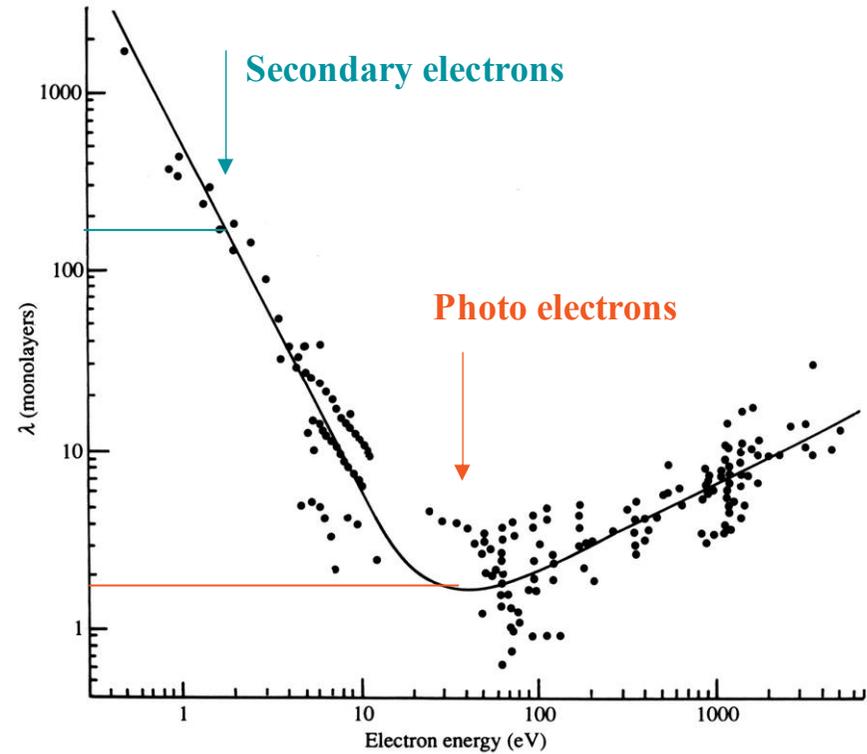
versus secondary electrons

valence band region

$h\nu = 48 \text{ eV}$

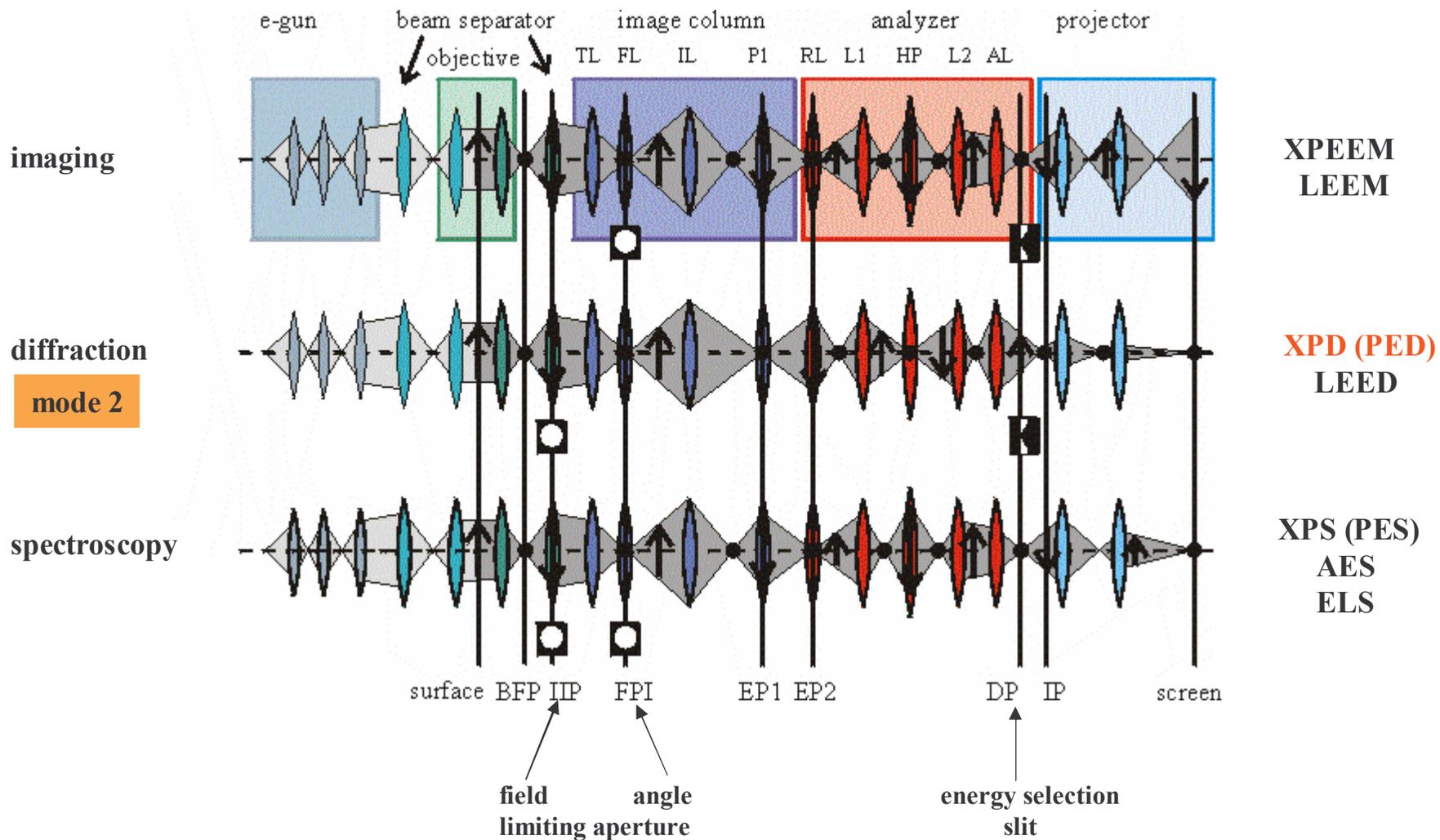


Pb on Si(111) – Ag ($\sqrt{3} \times \sqrt{3}$) – R30°
(1 monolayer Ag)



Inelastic mean free path
("universal curve")
determines sampling depth

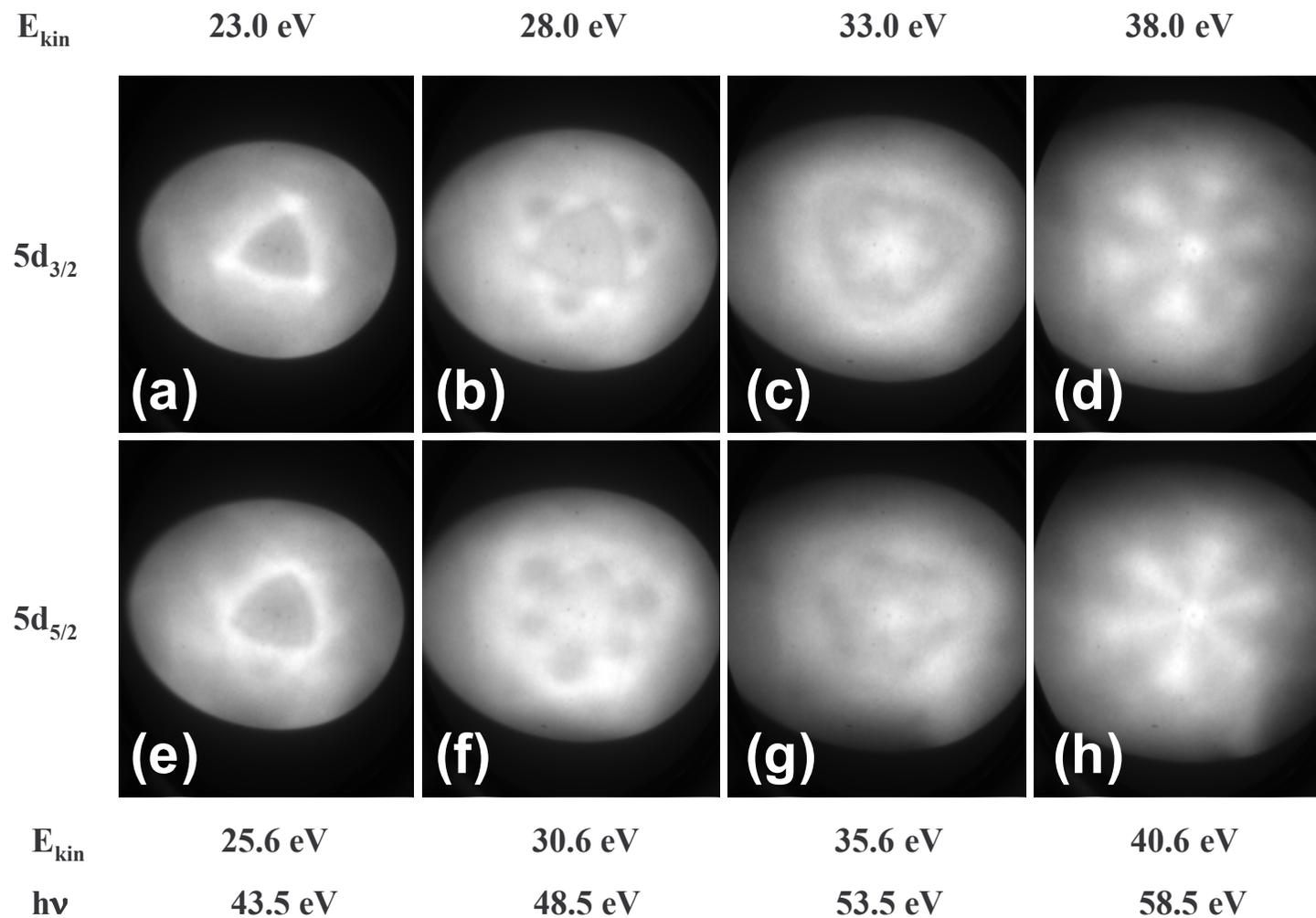
Operation modes of a SPELEEM



Local photo electron diffraction (mode 2)

Pb 5d photo electrons

from 0.8 μm^2 area (selected field aperture)

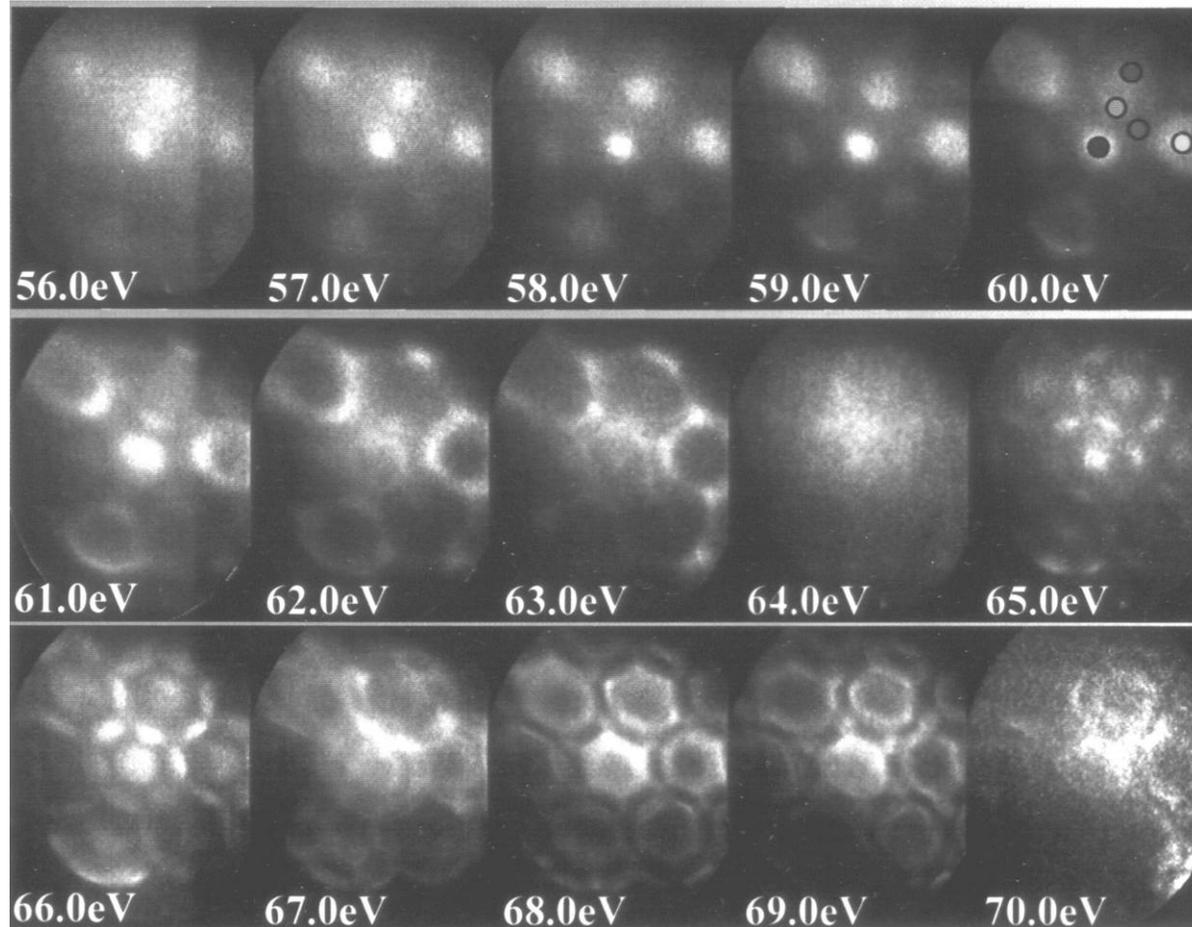


Local band structure analysis (mode 2)

Conduction band of Pb(111)

5 Pb monolayers on Si(111) – Au $\sqrt{3}\times\sqrt{3}$ – R30°

$h\nu = 73$ eV, $0.8 \mu\text{m}^2$ area (selected field aperture)

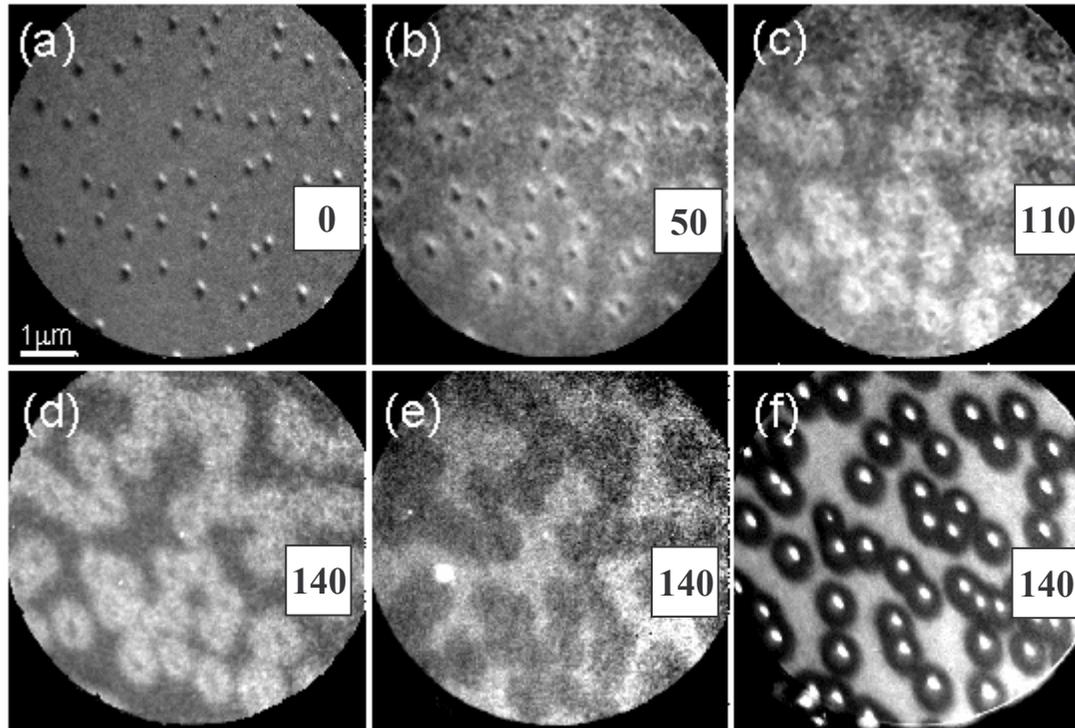


Parameter: E_{kin}

Application examples

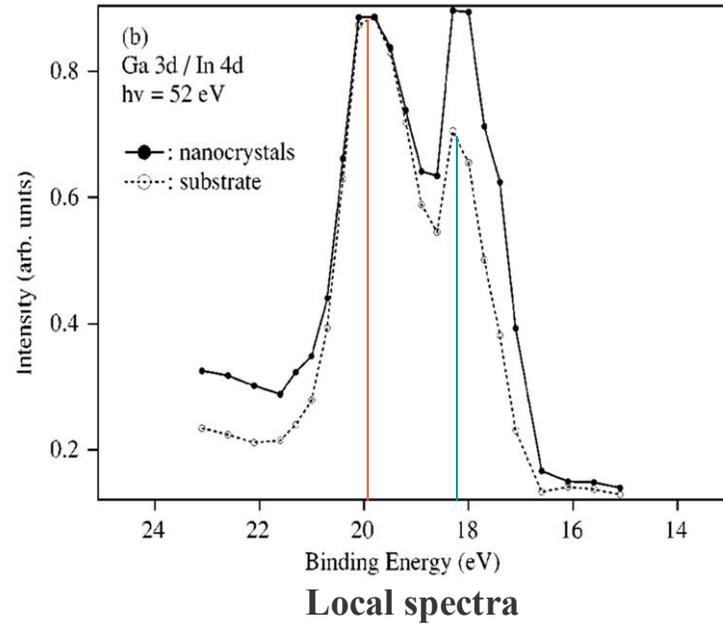
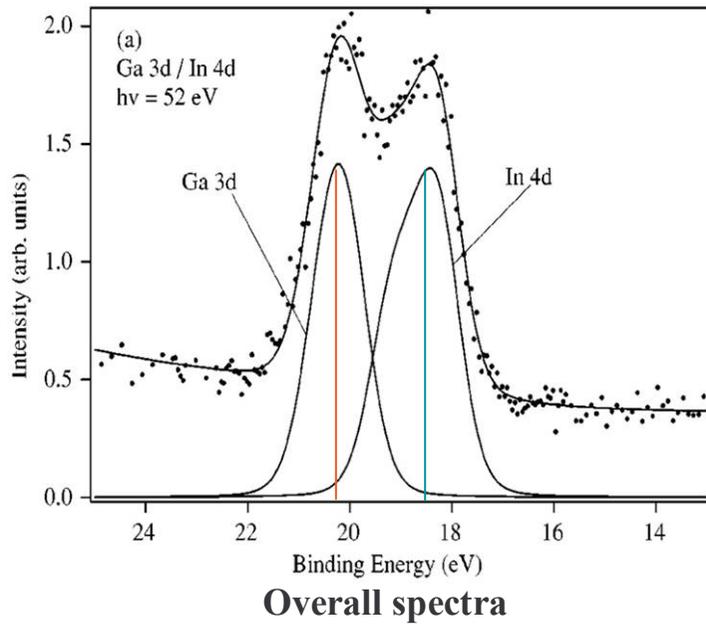
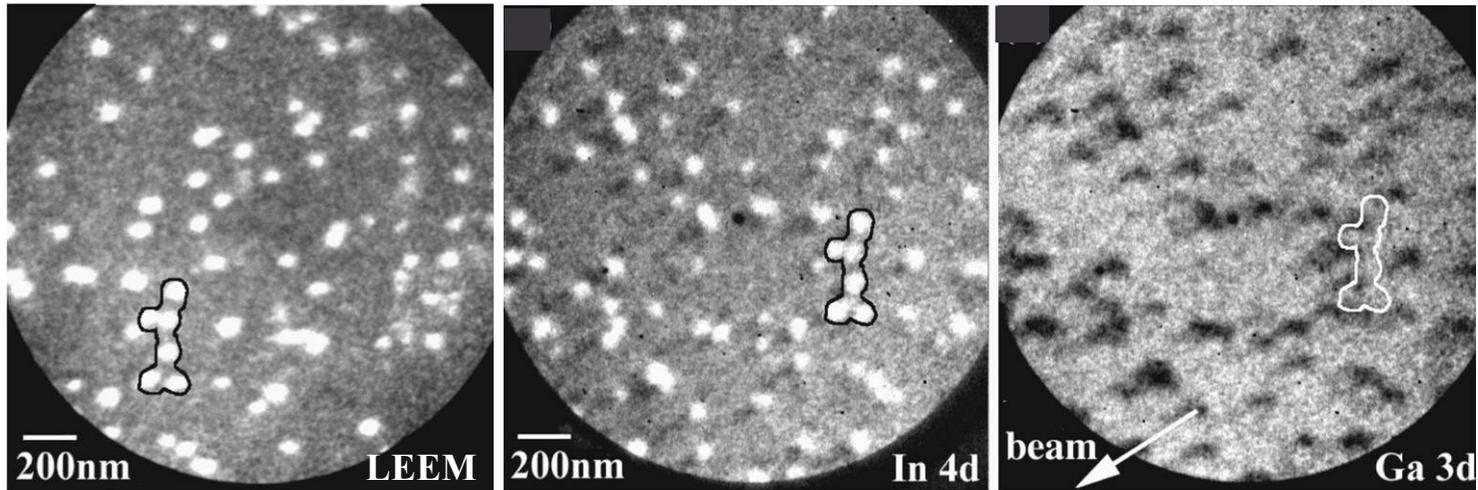
Fe on Pb on W(100)

Surfactant action



(a) – (d) Pb 5d images ($h\nu = 70.5$ eV, $E_{\text{kin}} = 49$ eV), (e) Fe 3d image, (f) LEEM image
270 K

InAs nanocrystals on Se-passivated GaAs(100)



Ga on nanocrystals, **In** on substrate
intermixing SK growth

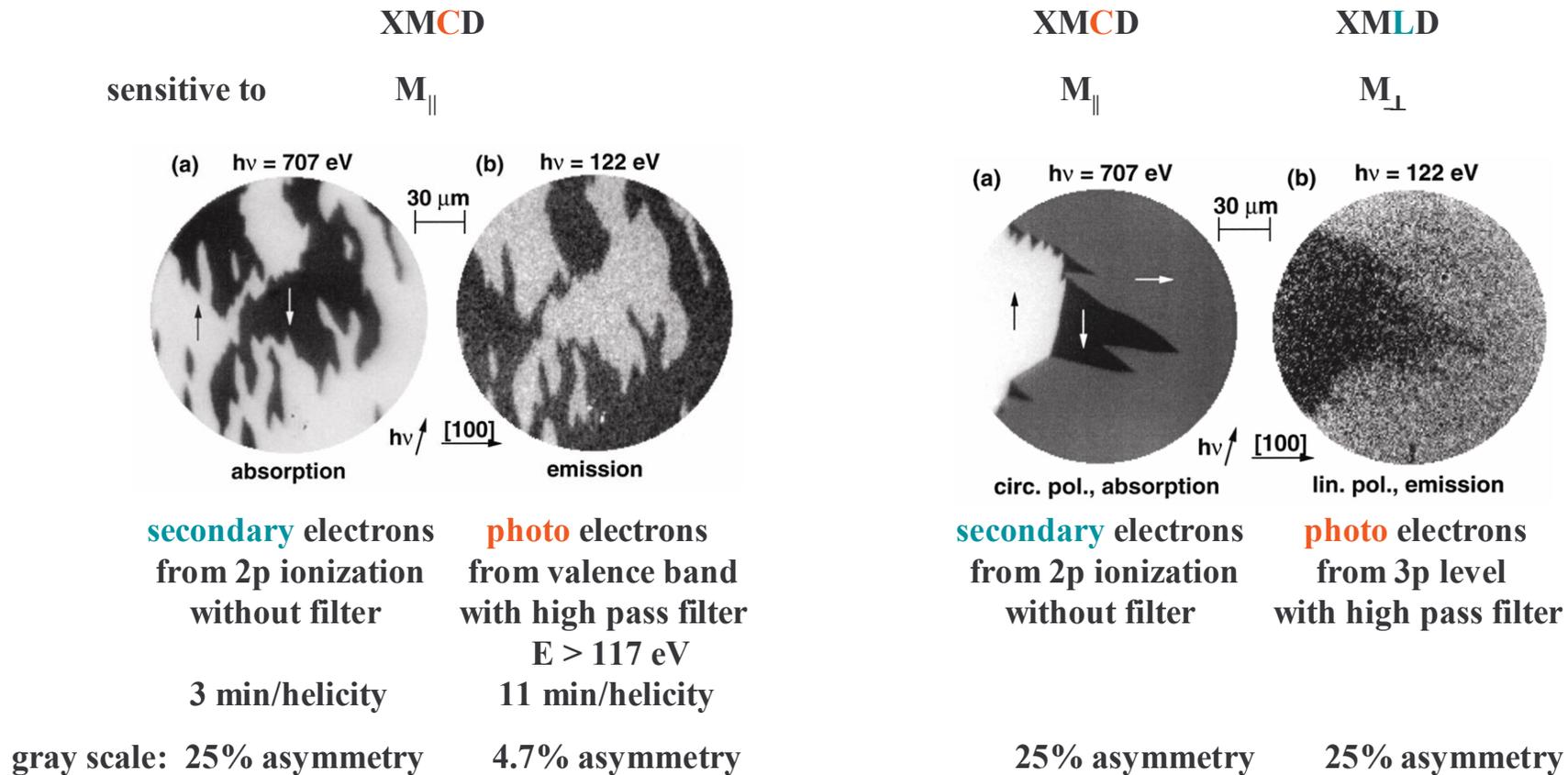
Magnetic imaging

XMCD, XMLD

Magnetic imaging in XPEEM

Ferromagnetism Imaging modes

Sample: 10 Fe monolayers on W (100)

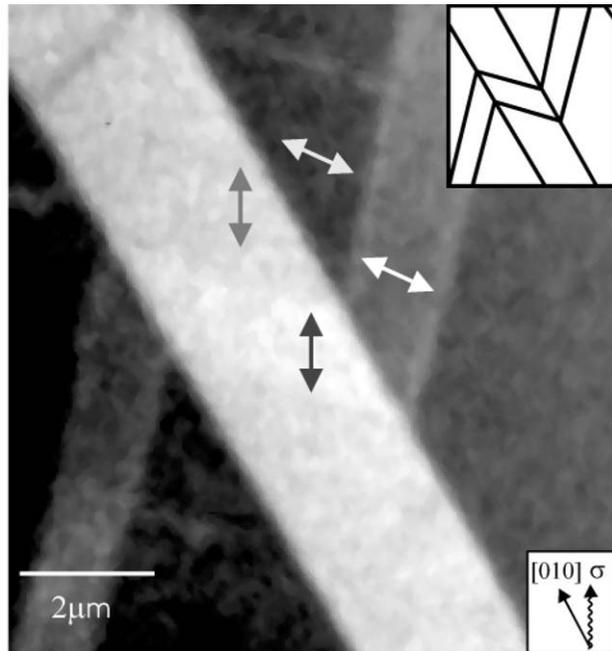


asymmetry: XMCD: $(I_{\sigma^-} - I_{\sigma^+}) / (I_{\sigma^-} + I_{\sigma^+})$ XMLD: $(I_l - I_h) / (I_l + I_h)$

Magnetic imaging with XPEEM

Antiferromagnetism and ferromagnetism

NiO (100)



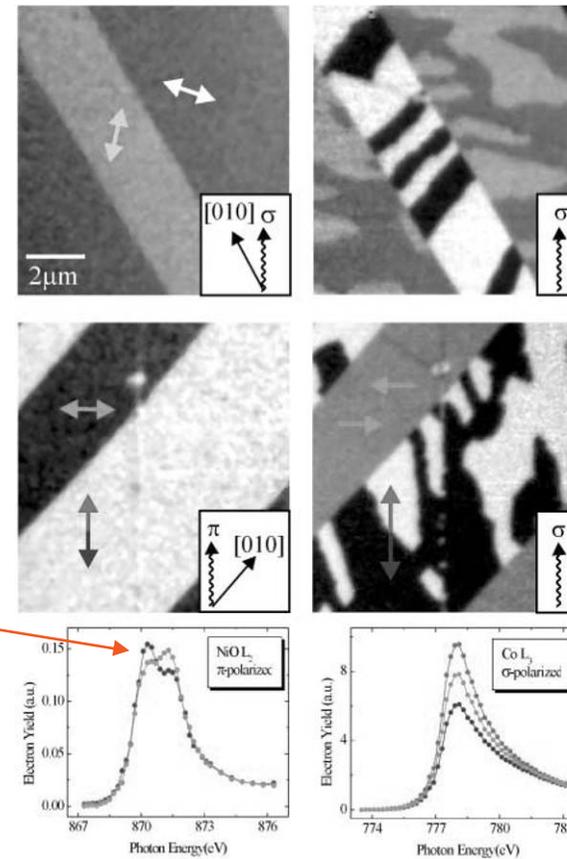
Contrast from intensity ratio of Ni L_2 doublet obtained with circular polarization (E_{\perp}/E_{\parallel}) σ
 Arrows: in-plane projections of AF axes obtained with linear polarization (E_{\parallel}) π

AF maximum contrast when $E \perp$ AF axis

8 Co monolayers on NiO (100)

AF domains
Ni L_2 images

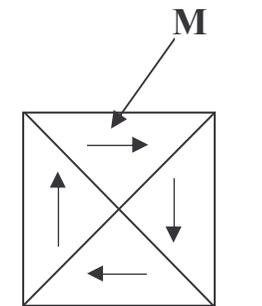
F domains
Co L_3 images



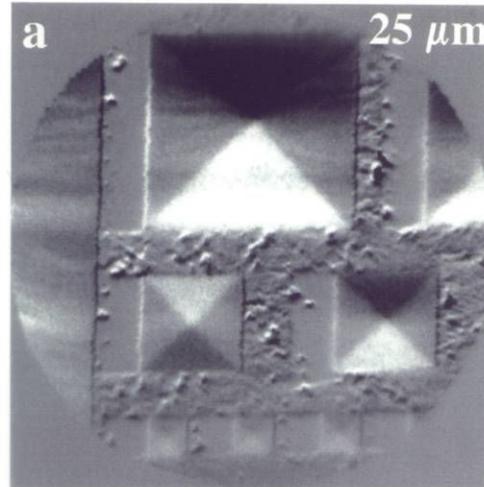
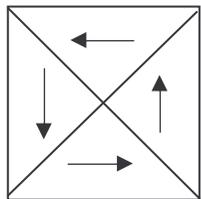
Exchange coupling

Closure domains in permalloy squares

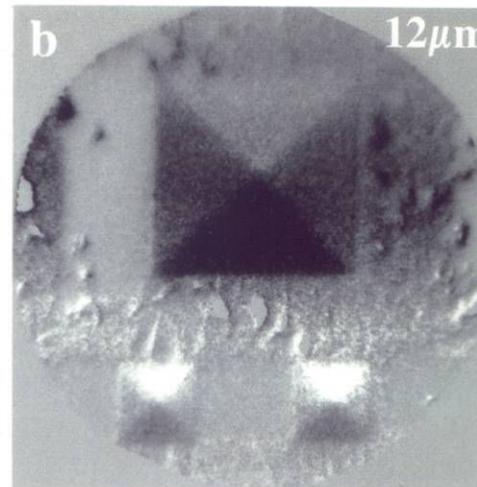
Ion beam milled from permalloy film



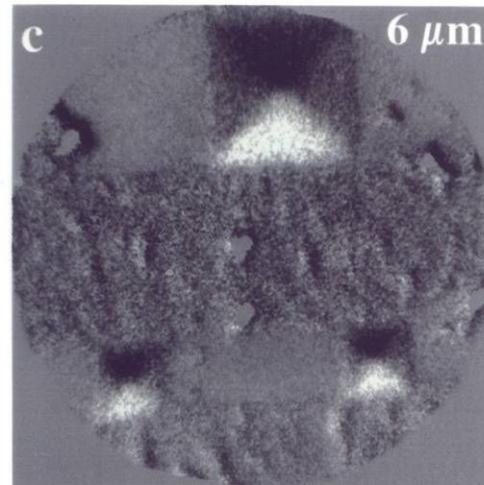
$h\nu$
→ σ
Fe L_3 edge



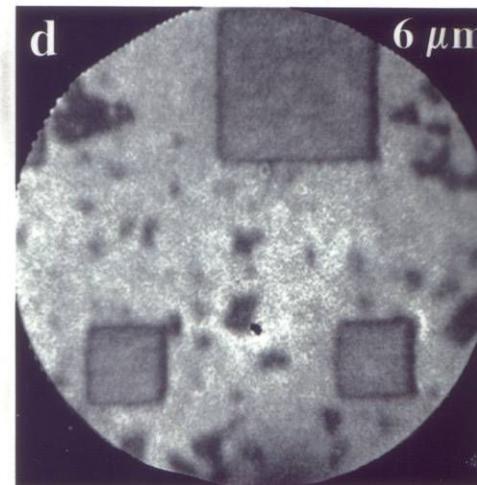
10 μm and 5 μm



5 μm and 2 μm



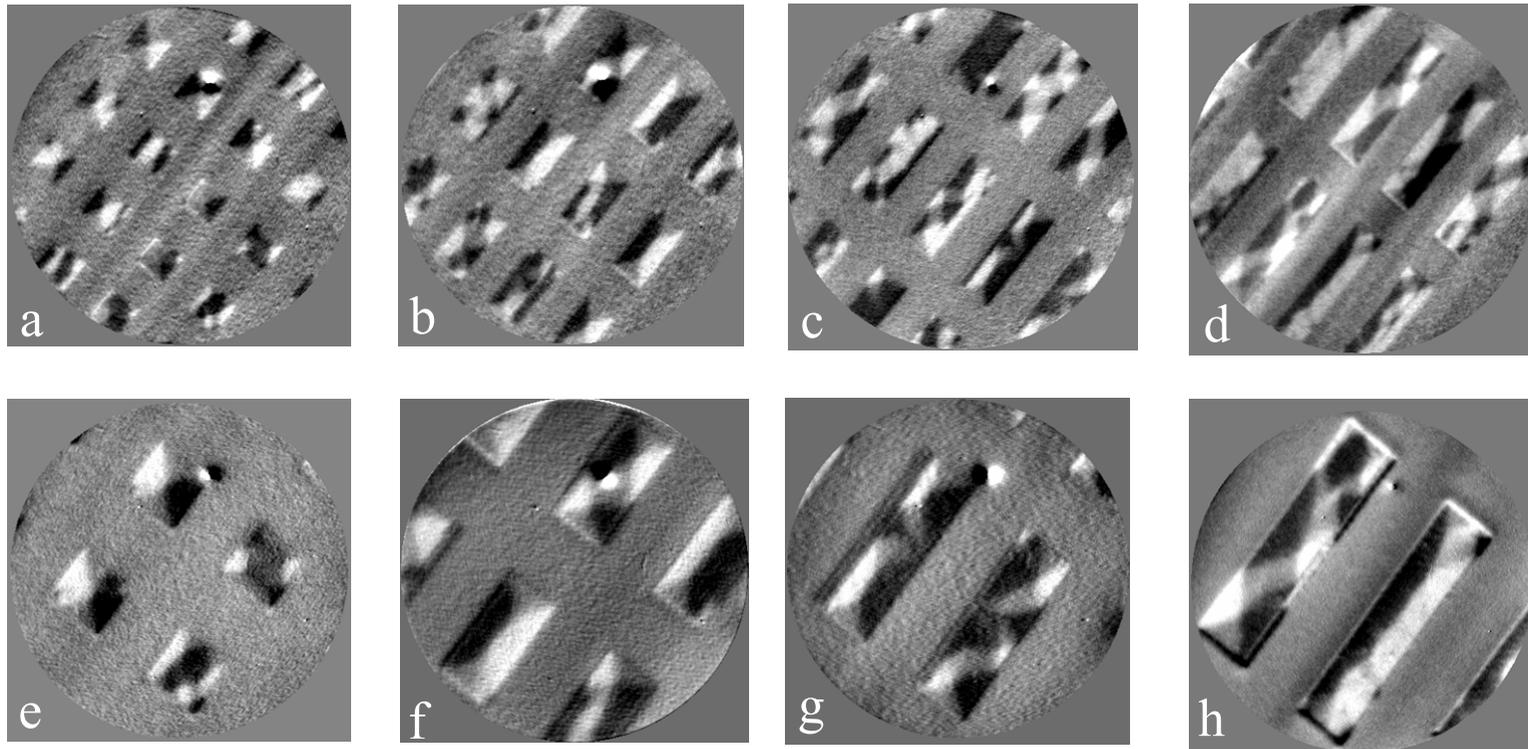
2 μm and 1 μm



2 μm and 1 μm (LEEM)

XMCDPEEM

Aspect ratio dependence of the virgin domain structure of 1 μm wide Co bits

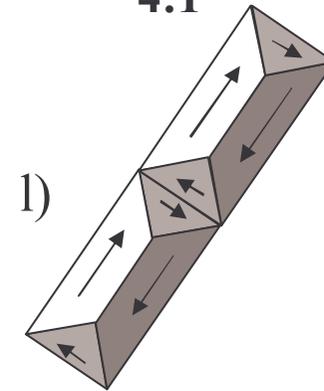
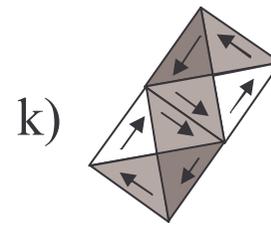
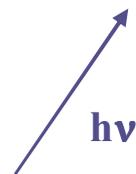
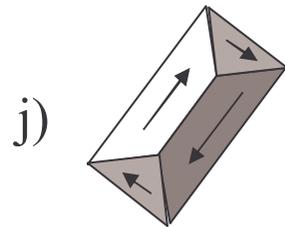
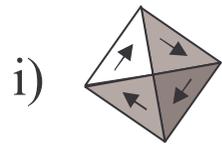


1:1

2:1

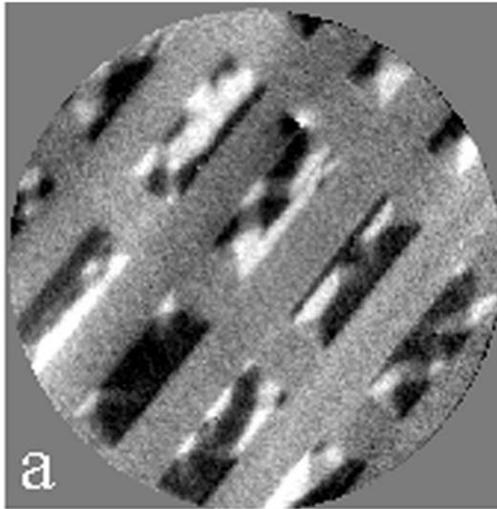
3:1

4:1

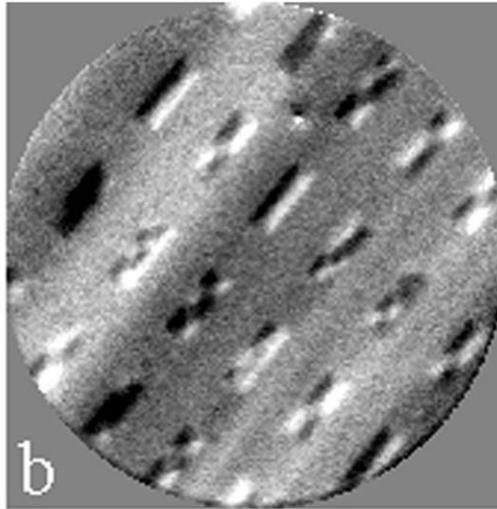


XMCDPEEM

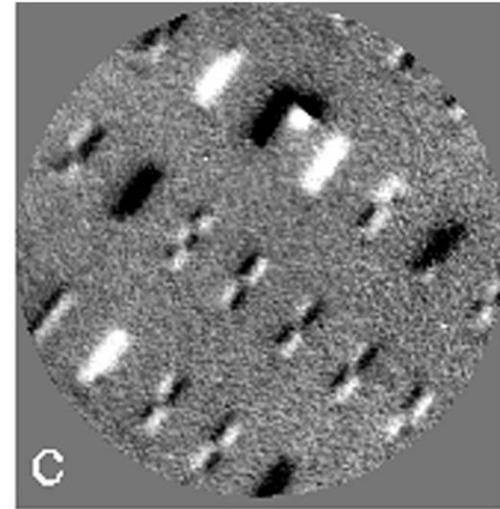
Size dependence of the domain structure of 15 nm thick Co bits
Aspect ratio 3:1, virgin state



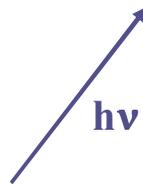
1000 nm



500 nm
width



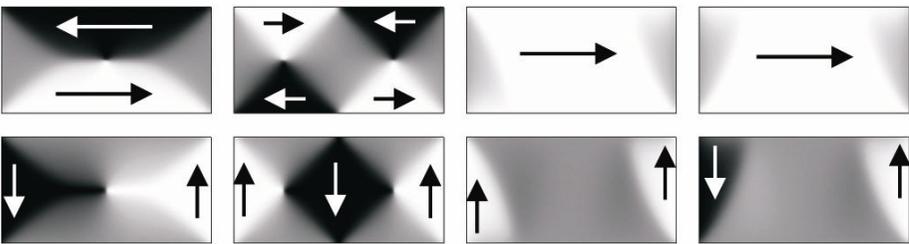
250 nm



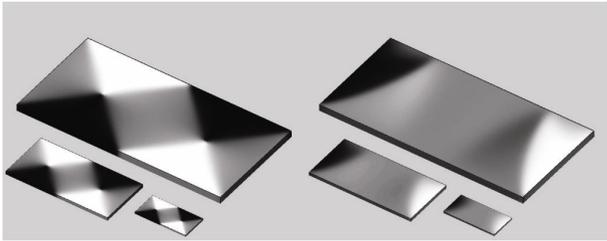
Micromagnetic simulations of permalloy bits with aspect ratio 2:1

R. Hertel, Z. Metallk. 93 (2002) 957

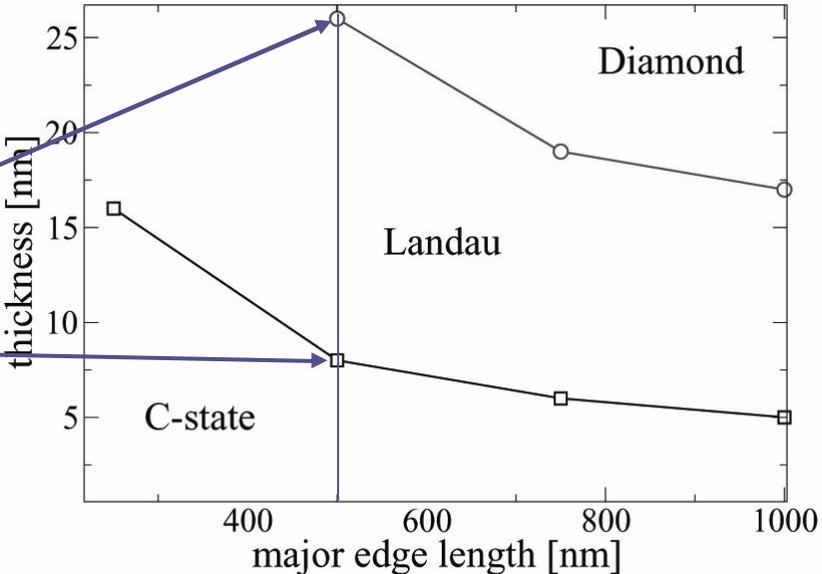
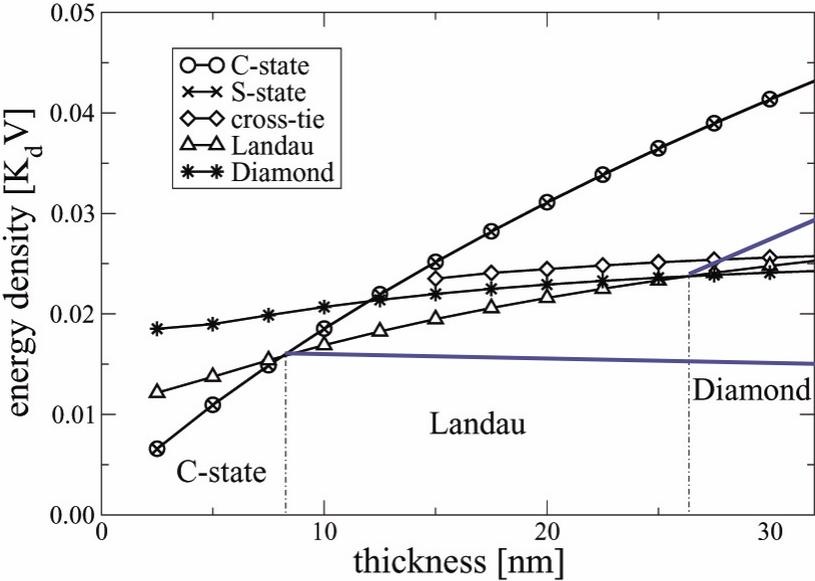
Landau diamond S C



Size independence

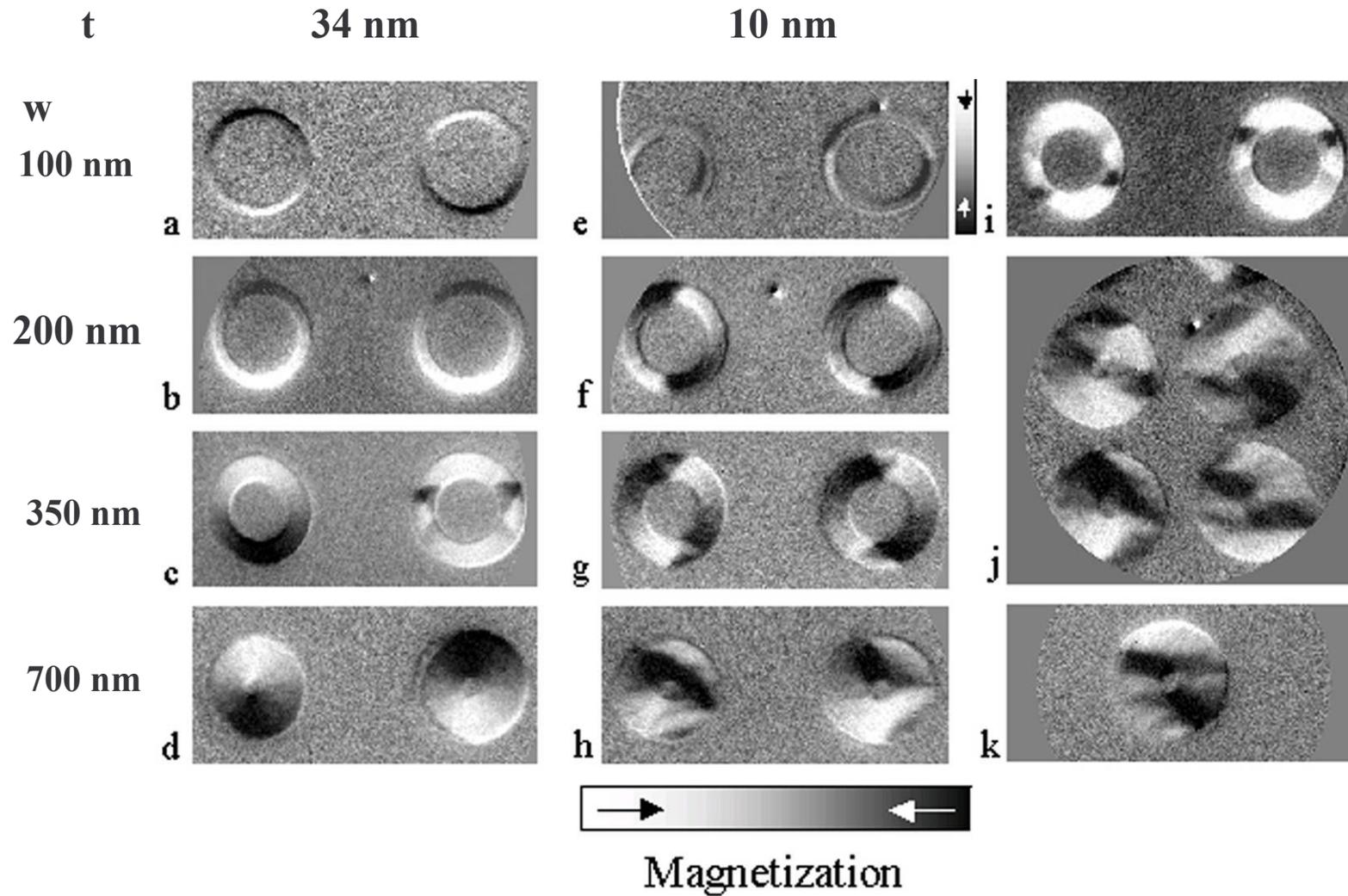


500 nm x 250 nm

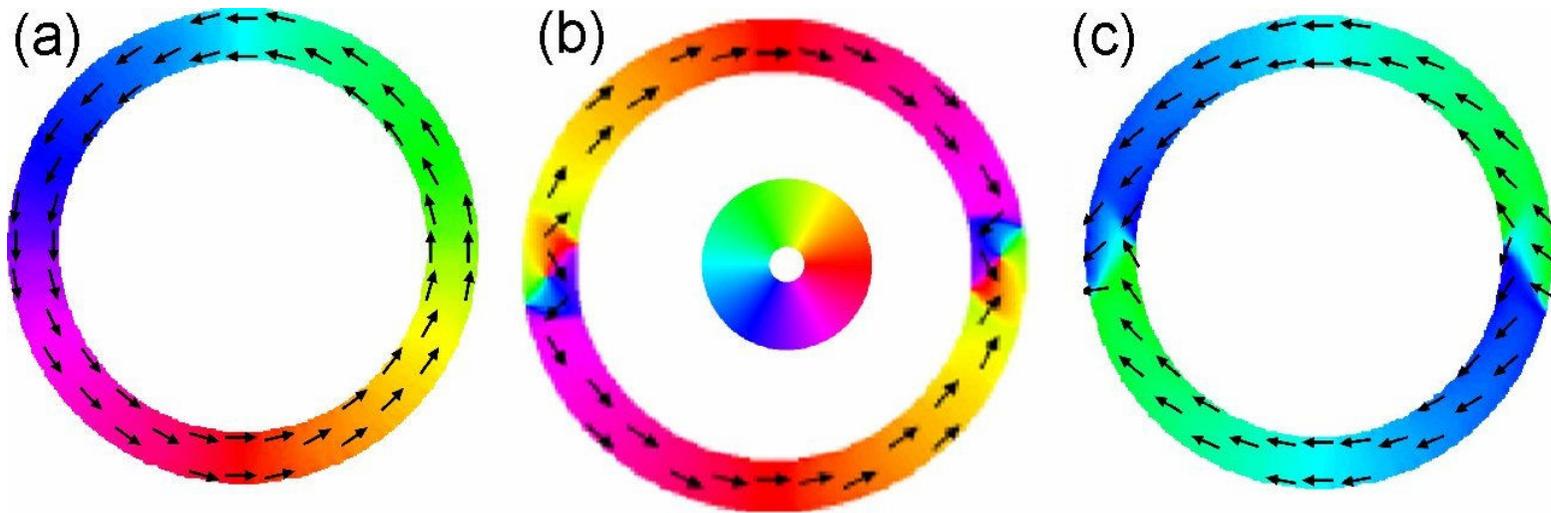


XMCDPEEM

Domain structure of 1.6 μm wide Co rings



Micromagnetic simulations of ferromagnetic rings



Vortex state

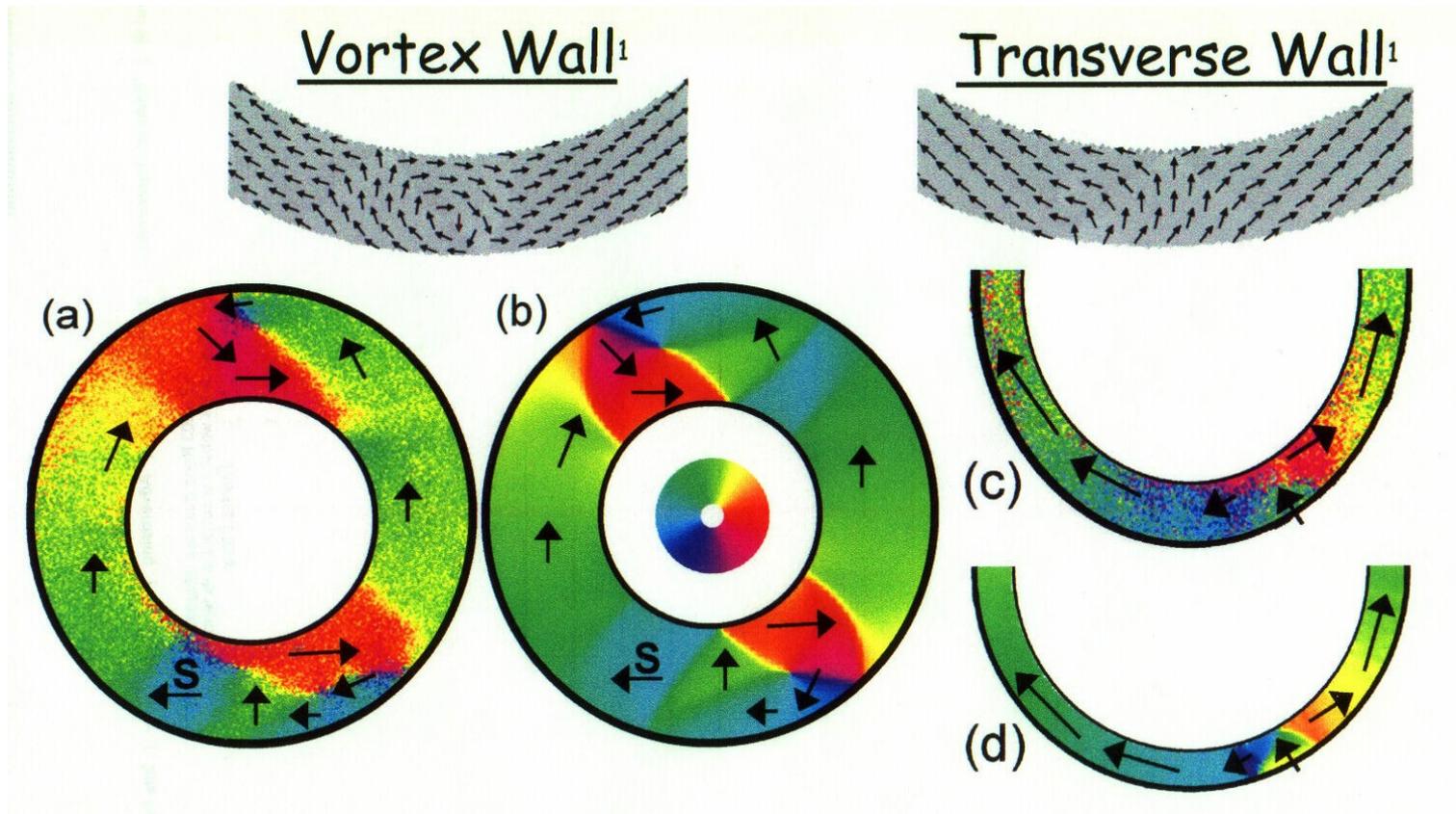
Onion states

Vortex walls

Transverse walls

M. Kläui, private comm.

Onion States



MnAs

Bulk properties

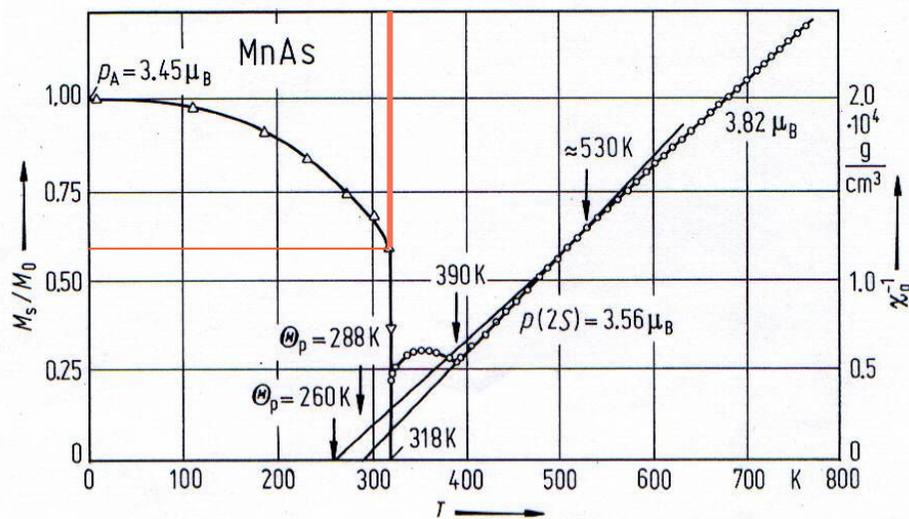
Magnetization

ferromagnetic

paramagnetic

α

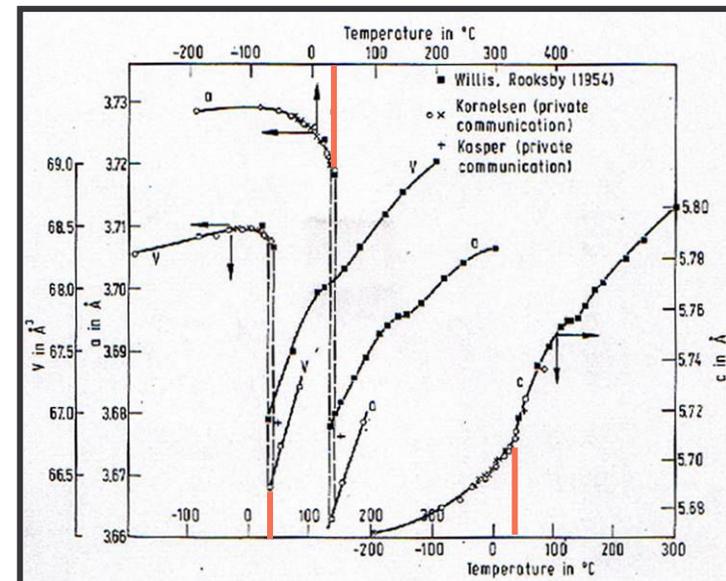
β



Sudden loss of magnetization
at structural transition

Thermal expansion

a , c , V



Large a contraction, little c expansion
at phase transition

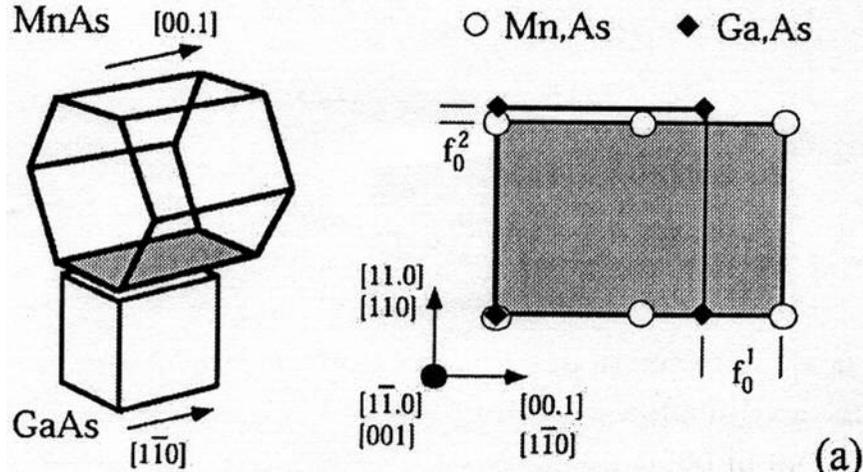
MnAs

- α $T < \approx 40$ °C NiAs (hexagonal) ferromagnetic
- β MnP (orthorhombic) paramagnetic
- γ $T > 125$ °C NiAs (hexagonal) paramagnetic

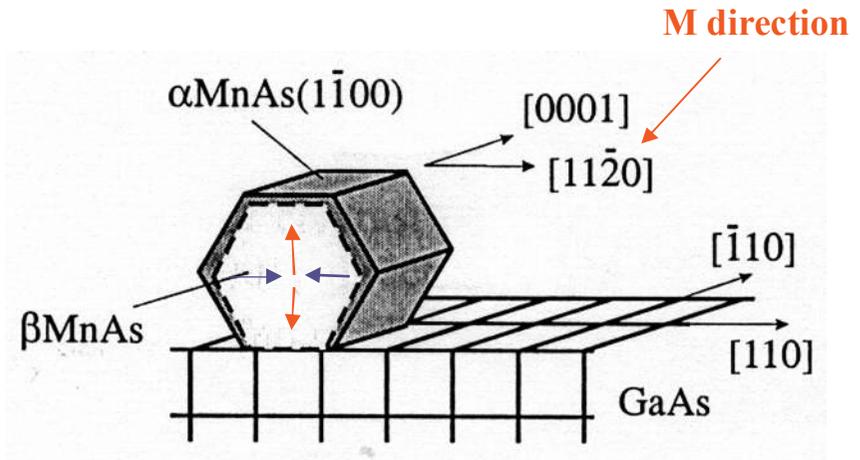


MnAs for spin injection into GaAs at room temperature?

Problem: **strain-induced phase coexistence** between ferromagnetic and paramagnetic phase around room temperature



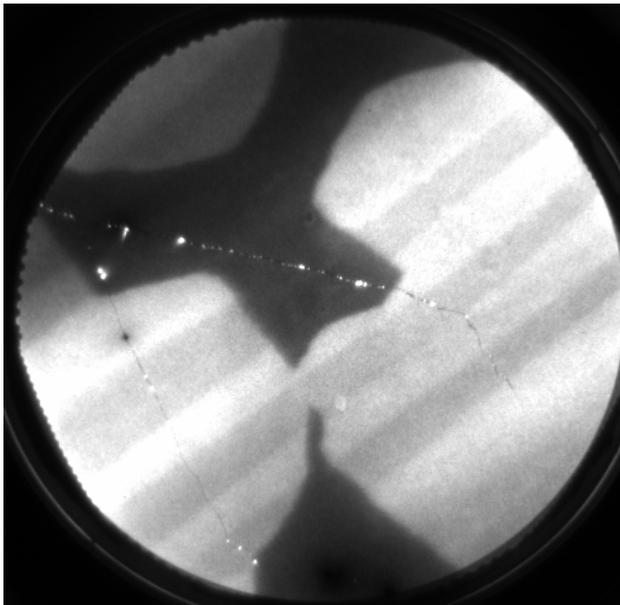
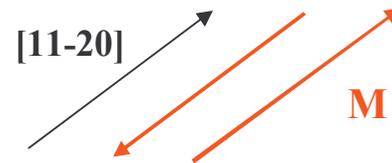
α MnAs / GaAs(100) $f_0^2 = 7.7\%$



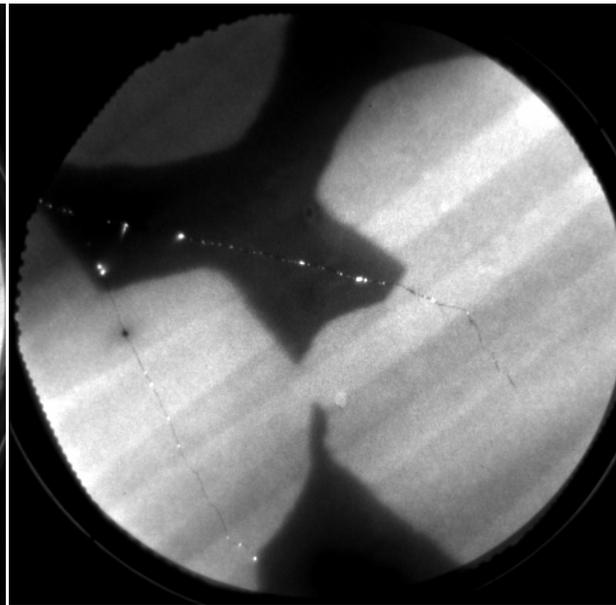
from L. Daeweritz et al ≥ 1999

Fully magnetized MnAs layer on GaAs (100)

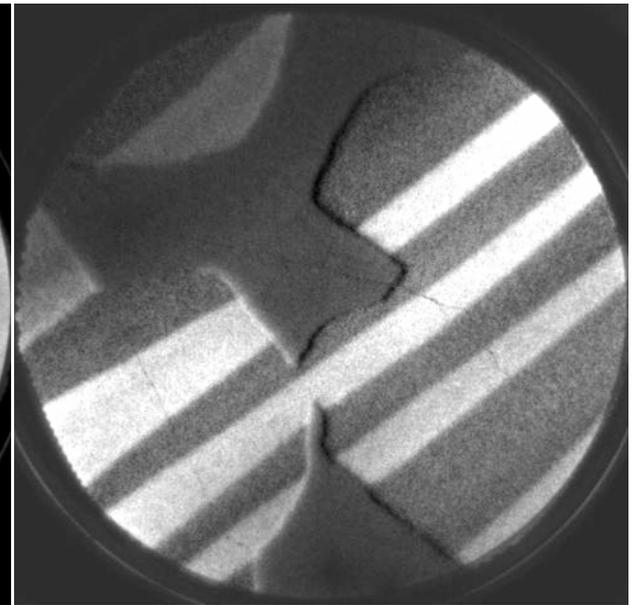
partially covered with As
magnetic contrast formation



helicity 1



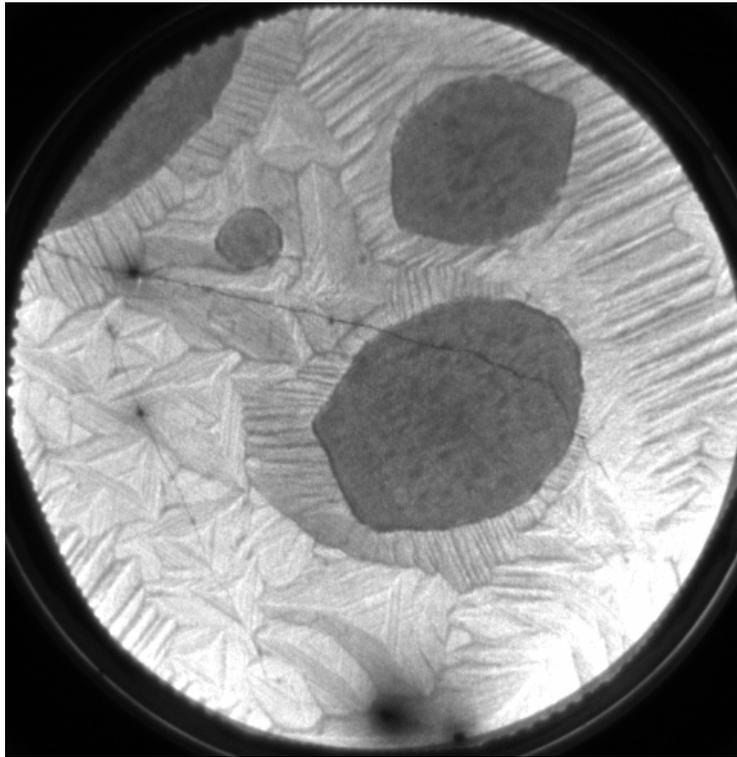
helicity 2



helicity 1 – helicity 2

1 μm

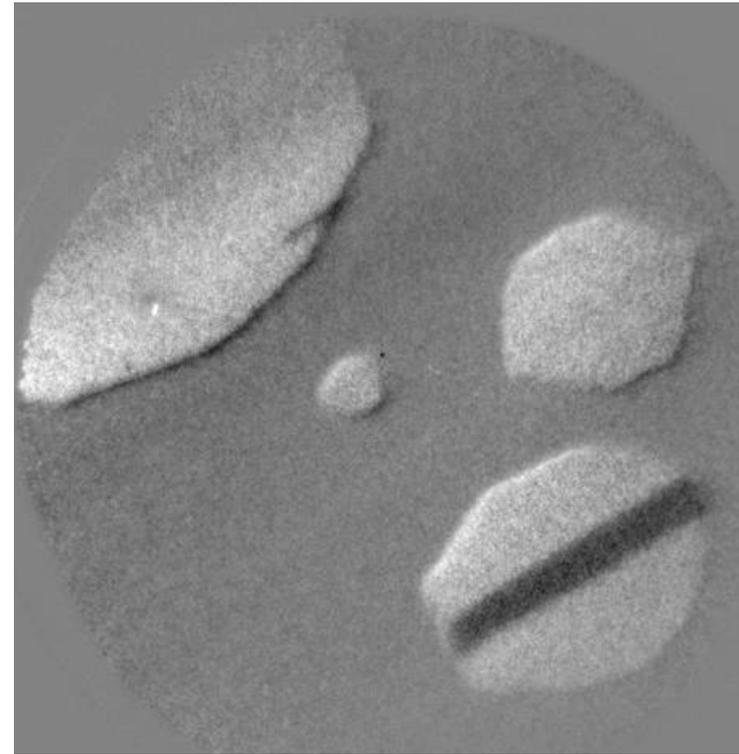
**MnAs islands on GaAs (100)
far below phase transition
surrounded by crystallized As capping**



10 eV

1 μm

LEEM

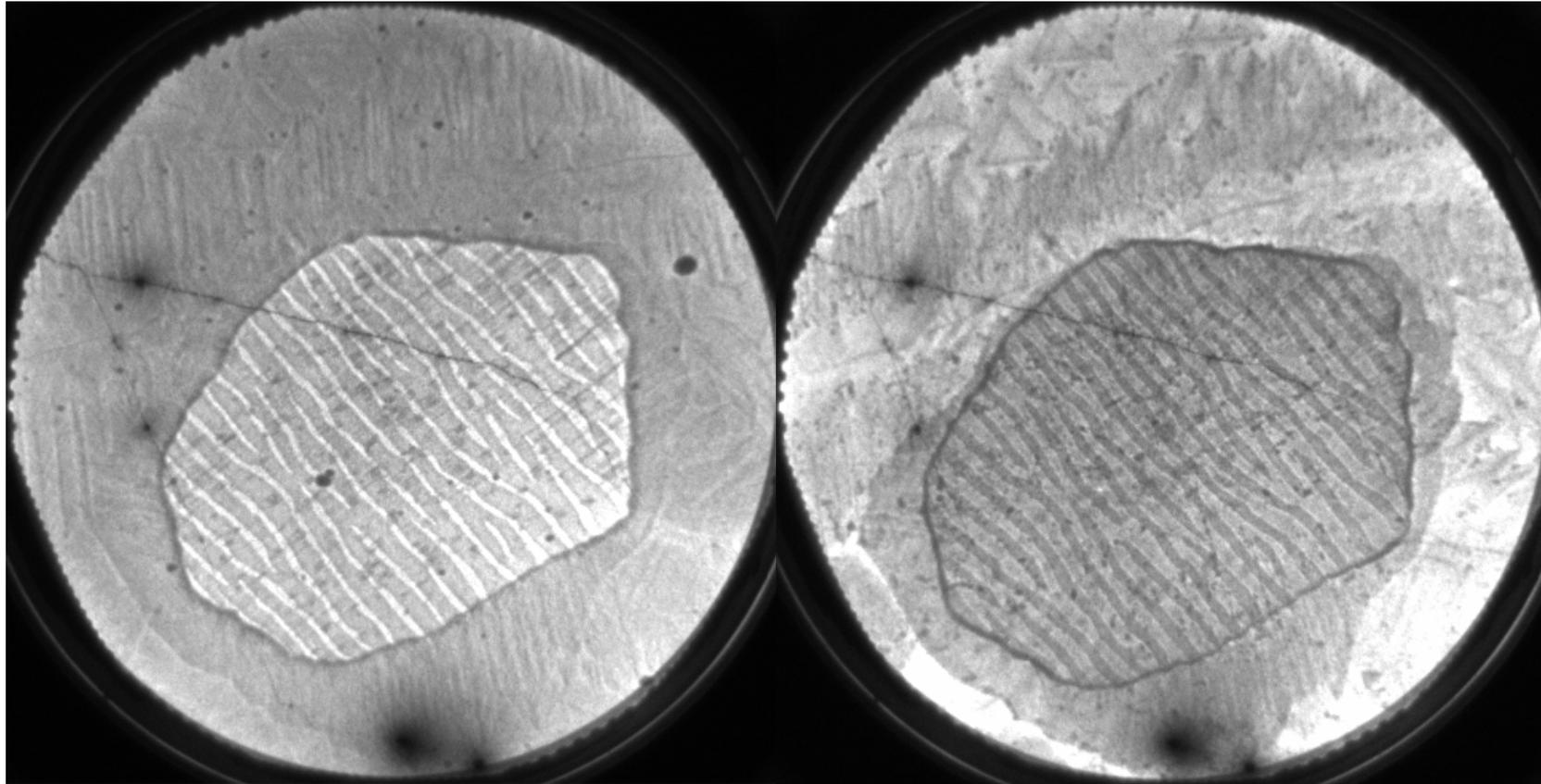


$h\nu = 639.5 \text{ eV}$

XMCDPEEM

MnAs islands on GaAs(100) in the phase transition region

Phase contrast
between hexagonal and orthorhombic phase



- 12 μm defocus

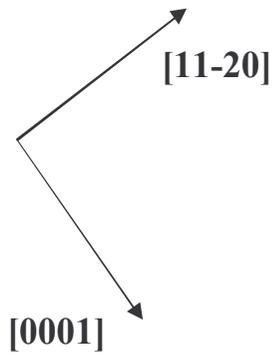
4.5 eV

+ 12 μm defocus

LEEM

1 μm

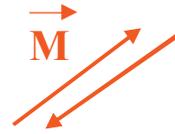




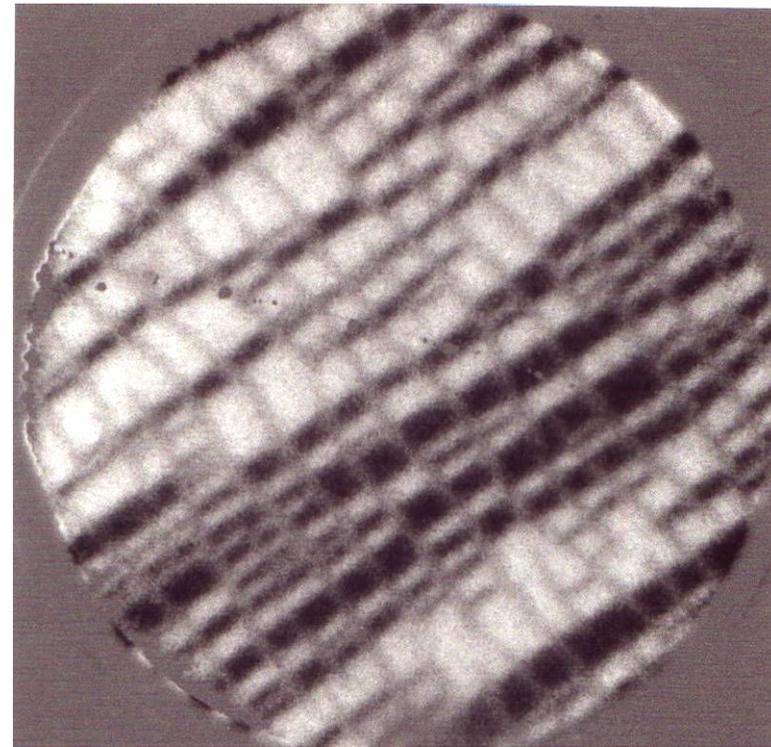
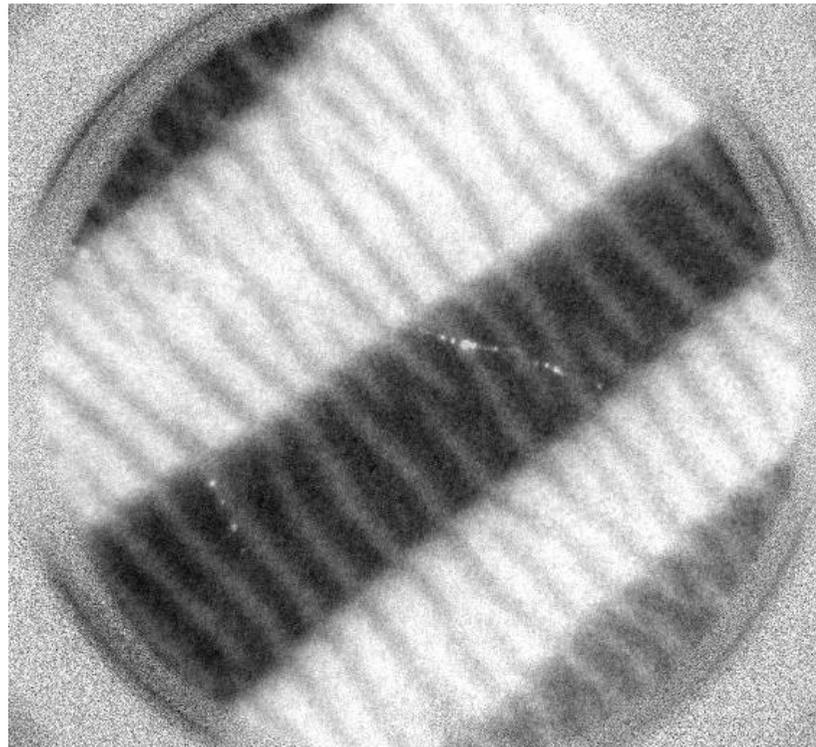
MnAs / GaAs(100) 40 nm

XMCDPEEM Mn 2p_{3/2} (639.5 eV)

during heating

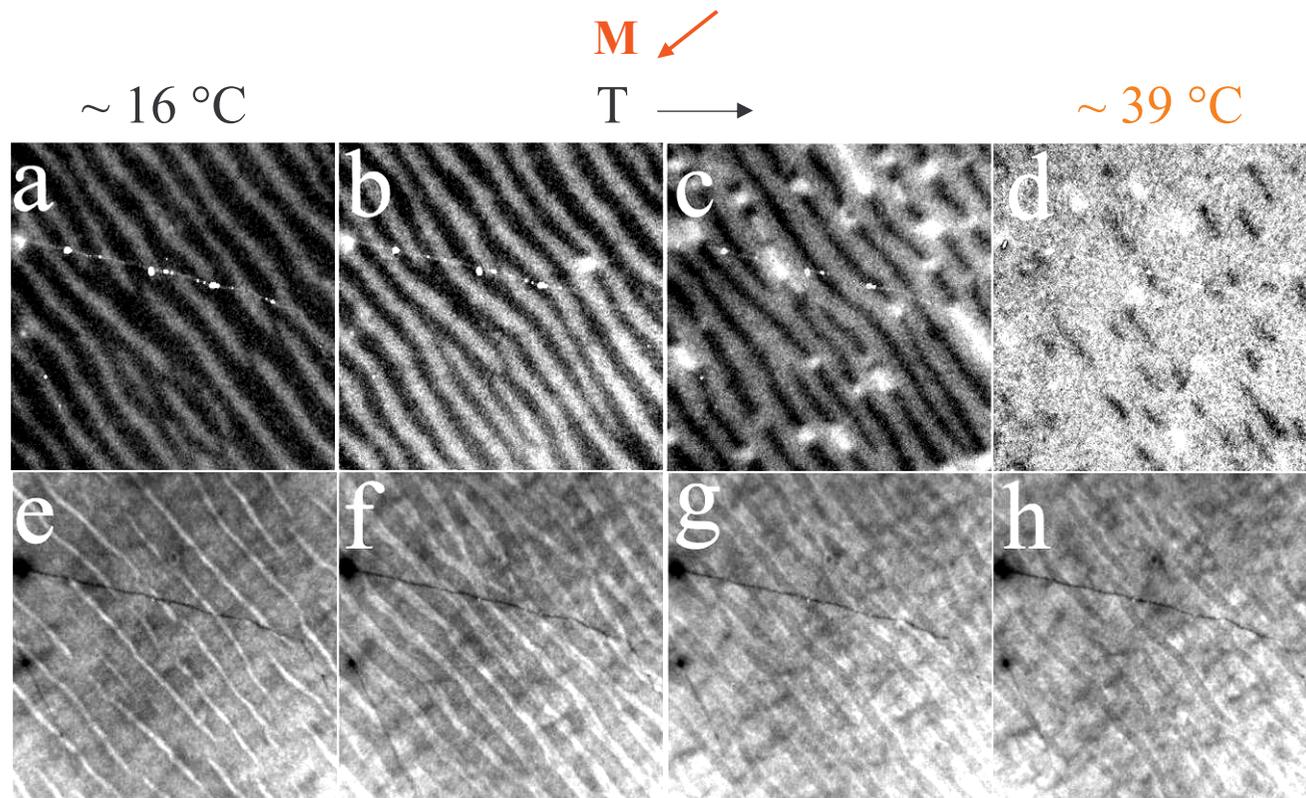


during cooling



1 μm

**Structural - magnetic phase transition
in 40 nm thick epitaxial MnAs layer on GaAs (001)**



a - d XMCDPEEM
MnL₃ (639.5 eV)

1 μm

e - h LEEM
4.5eV

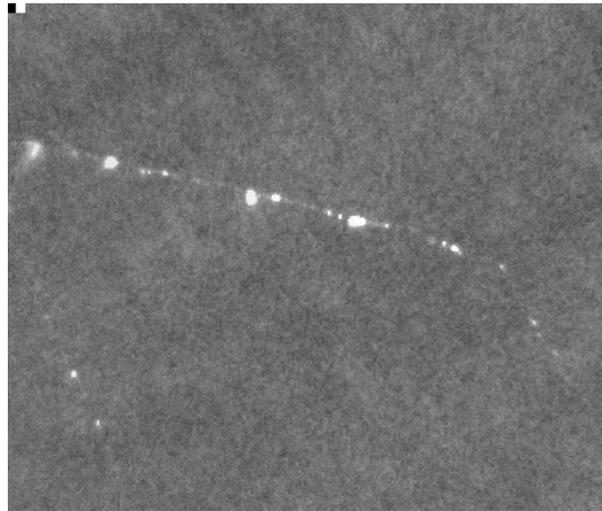
MnAs / GaAs(100)

Thickness 40 nm

Ferromagnetic – paramagnetic phase transition

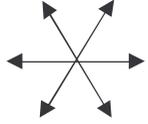
$\approx 13\text{ }^{\circ}\text{C}$ - $\approx 35\text{ }^{\circ}\text{C}$

black **M** 
white **M** 
gray paramagnetic



Field of view $4 \times 4\text{ }\mu\text{m}^2$

$\vec{M} \langle 11\bar{2}0 \rangle$

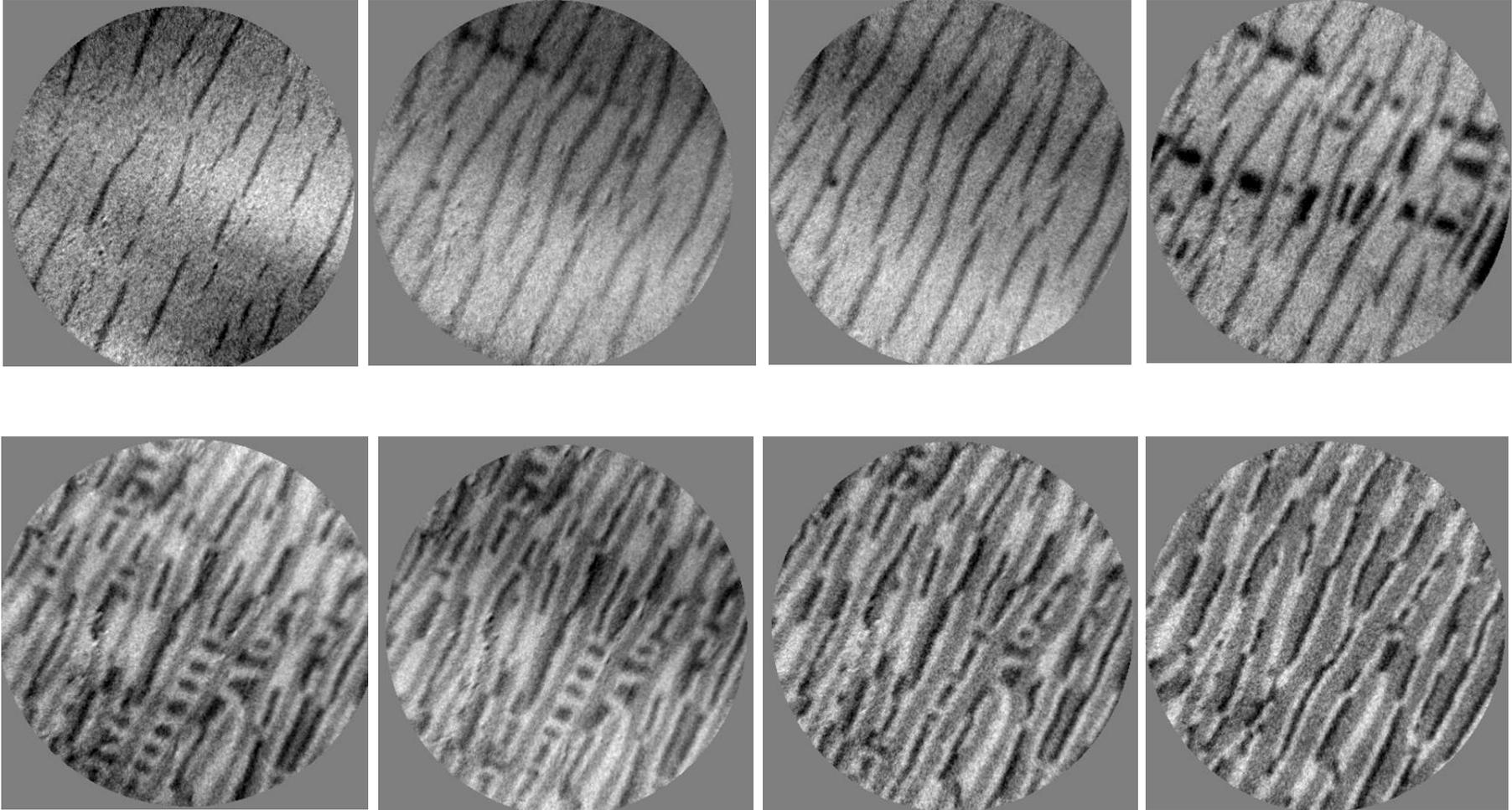


$[1-100]$

MnAs / GaAs (100)

Thickness 250 nm

T



white

\vec{M}

black

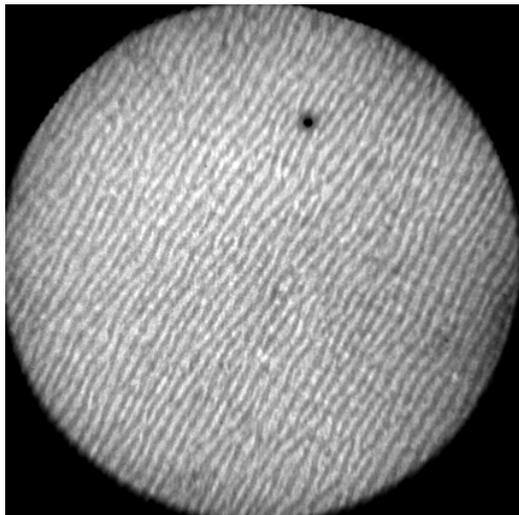
\vec{M}

1 μm

MnAs on GaAs(100)
Thickness dependence of stripe period
Structural images (LEEM)

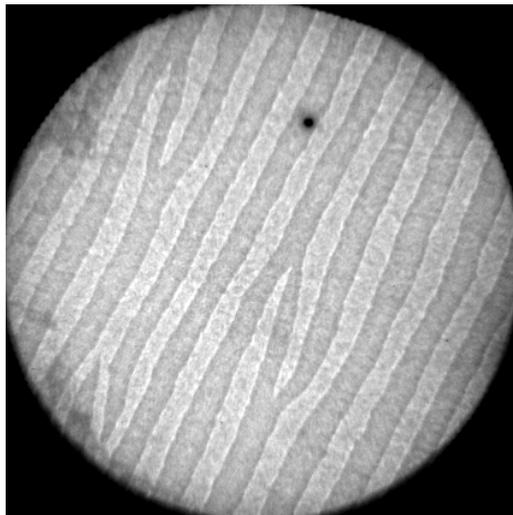
Diameter of field of view

10 μm



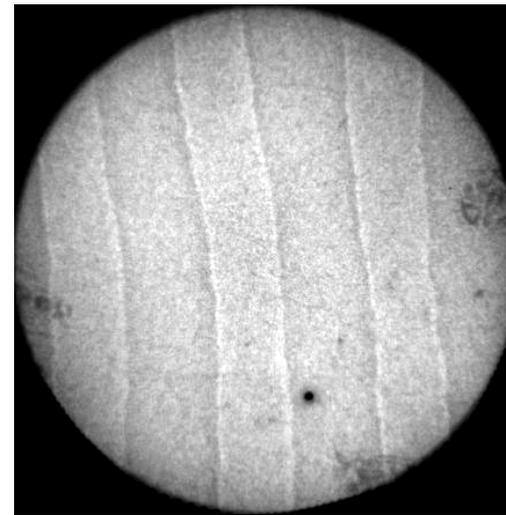
50 nm

10 μm



180 nm

5 μm

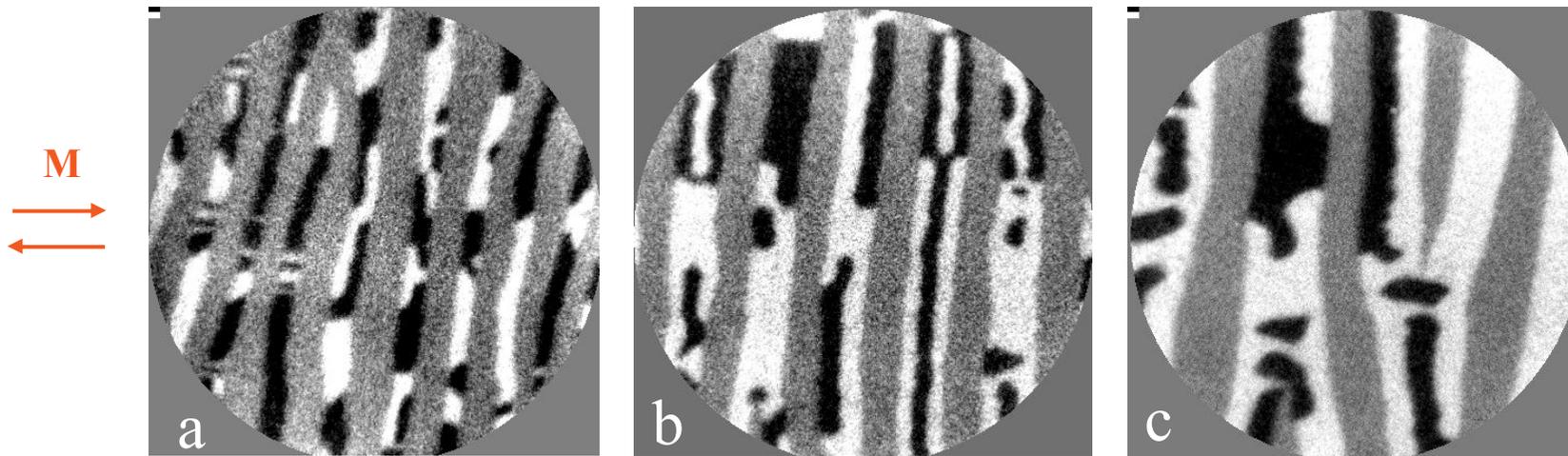


300 nm

MnAs on GaAs(100)

Thickness dependence of magnetic domain structure

Room temperature



120 nm

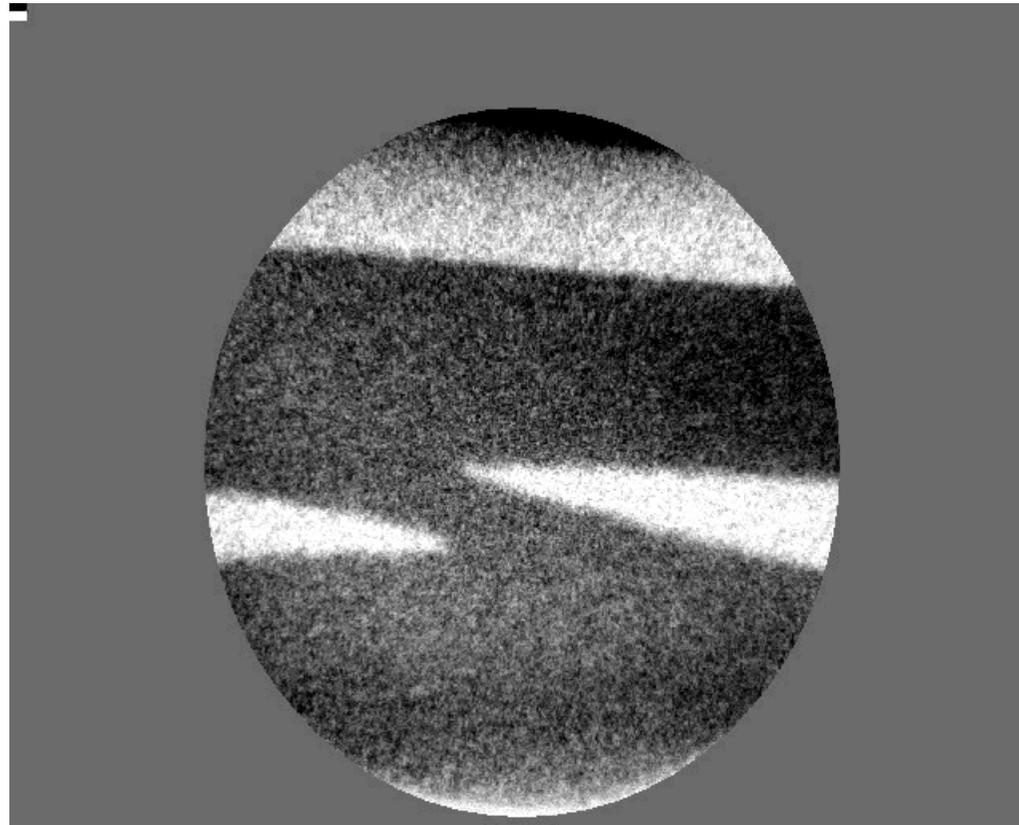
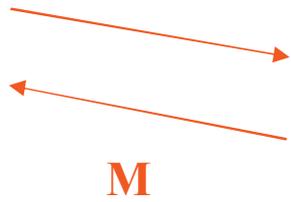
180 nm

300 nm

Field of view 5 μm diameter

MnAs on GaAs(100)

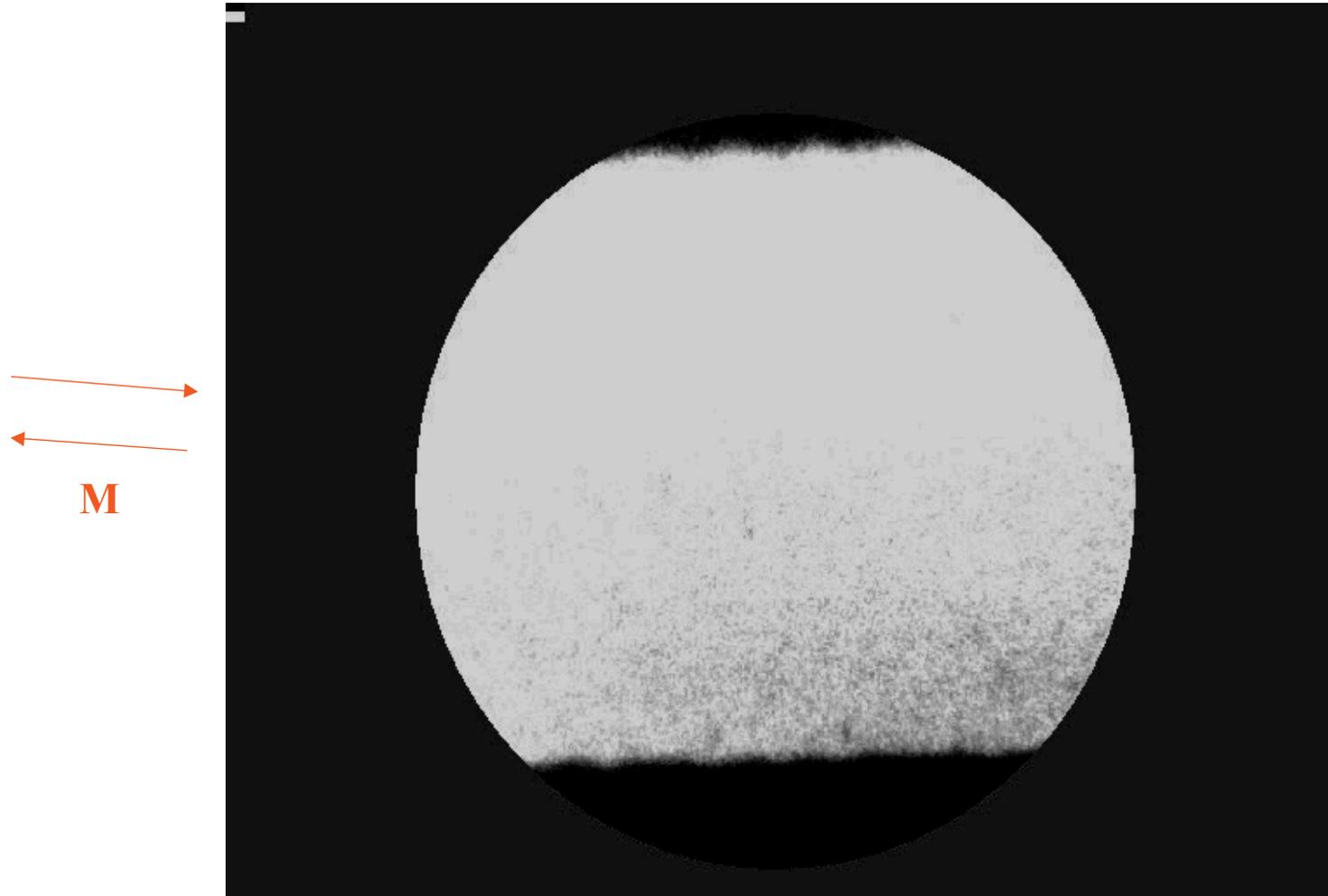
Thickness 120 nm
heating



Field of view 5 μm diameter

MnAs on GaAs(100)

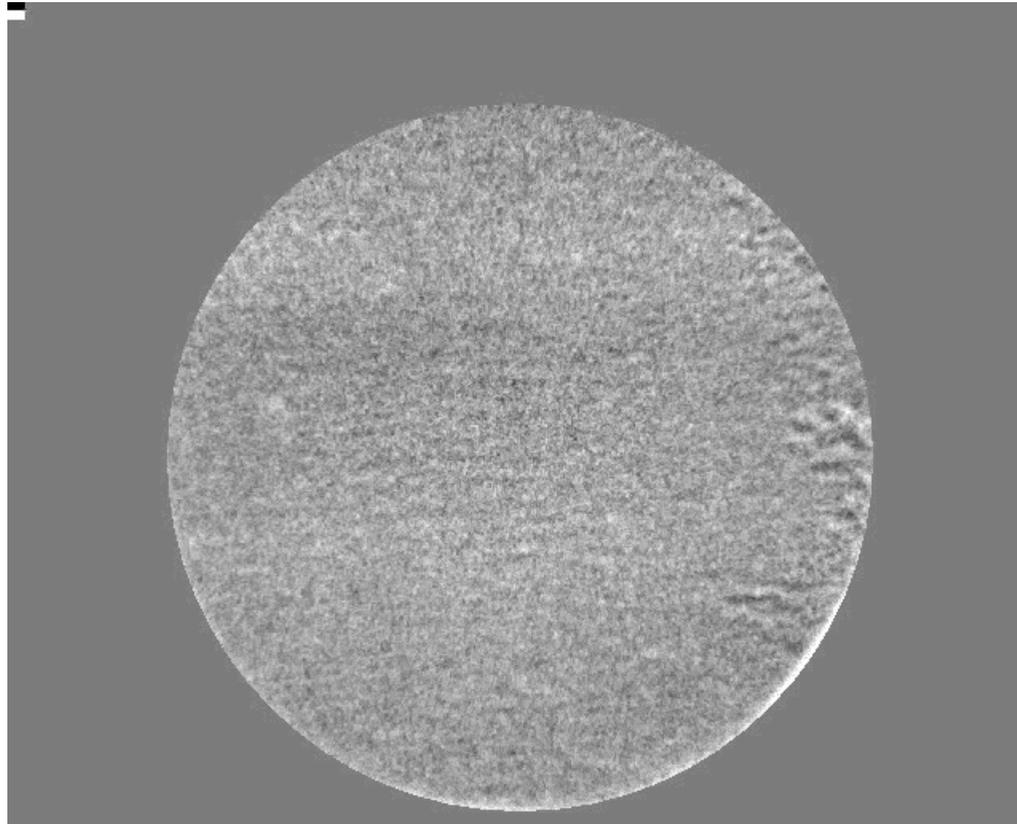
Thickness 180 nm
heating



Field of view 5 μm diameter

MnAs on GaAs(311)

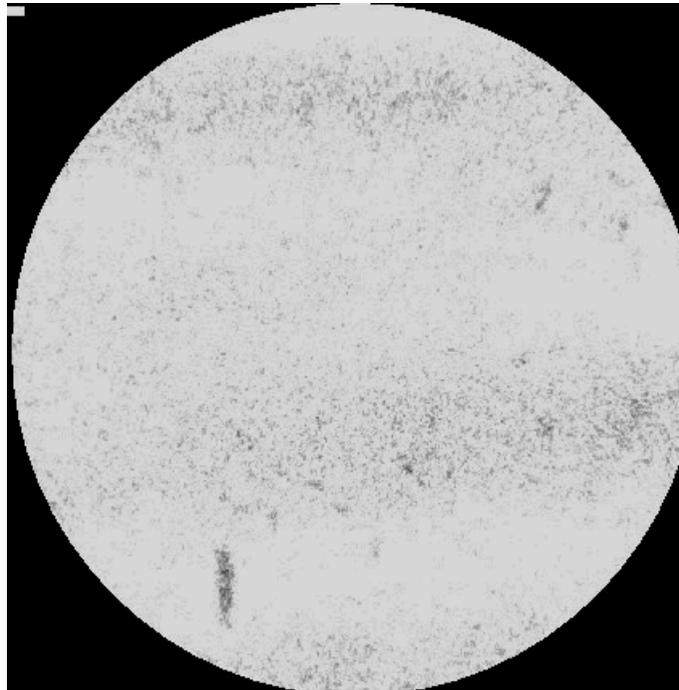
**Thickness 180 nm
cooling**



Field of view 5 μm diameter

MnAs on GaAs(100)

**Thickness 300 nm
heating**



Field of view 5 μ m diameter

General references

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E. Bauer, T. Franz, C. Koziol, G. Lilienkamp and T. Schmidt: *Recent Advances in LEEM/PEEM for Structural and Chemical Analysis*, in: *Chemical, Structural and Electronic Analysis of Heterogeneous Surfaces on Nanometer Scale*, ed. R. Rosei (Kluwer Acad. Publ., Dordrecht 1997) p. 73- 84

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